Laboratory Work 1
Simple semiconductor device circuits design and simulation

Nikolay Nikolaev (nanikolaev@itmo.ru)
Nikolai Poliakov (polyakov_n_a@itmo.ru)
Roman Olekhnovich (r.o.olekhnovich@mail.ru)

Summary

1. LT Spice simulation for electronic device analysis
2. Diode parameters analysis
3. Rectifier scheme simulation
4. Capacitor parameter analysis
5. Overvoltage test
6. Starting current test
7. Uploading report to the

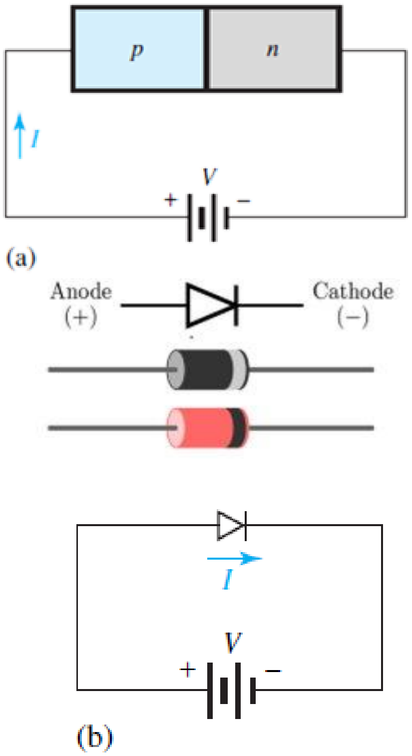
Goal and tasks

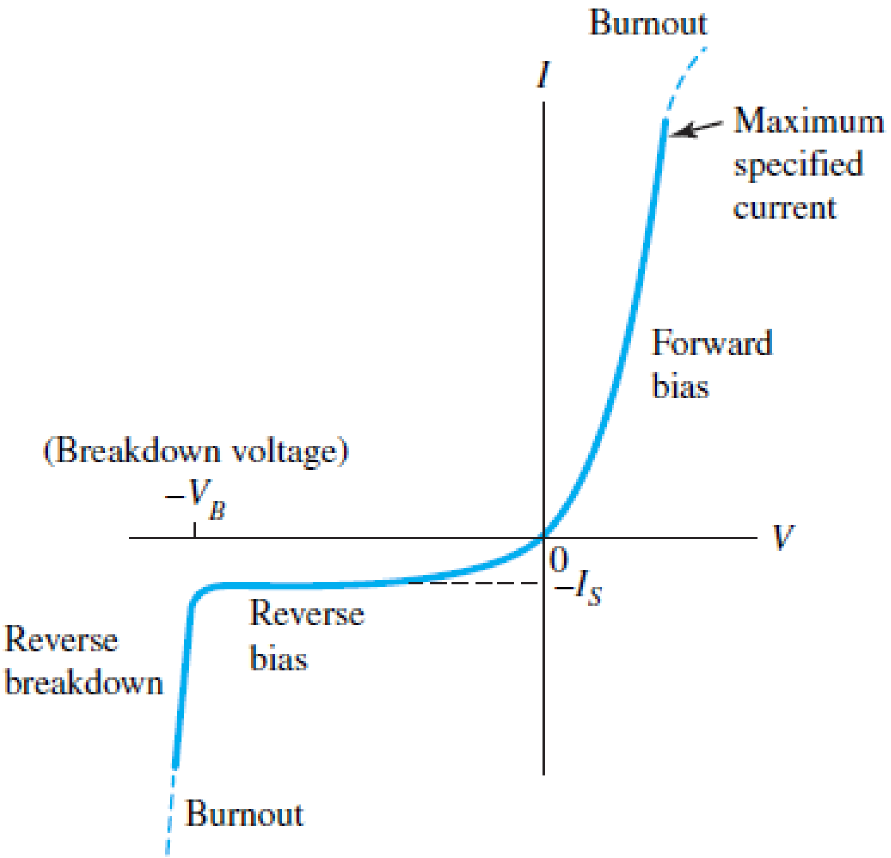
The goal of laboratory work «Simple semiconductor device circuits design and simulation» is to study rectifier scheme on the basis of proposed diode.

Laboratory work task are:

1. Rectifier scheme simulation
2. Diode parameters analysis
3. Capacitor parameter analysis
4. Overvoltage check
5. Starting current check

pn-junction under external voltage





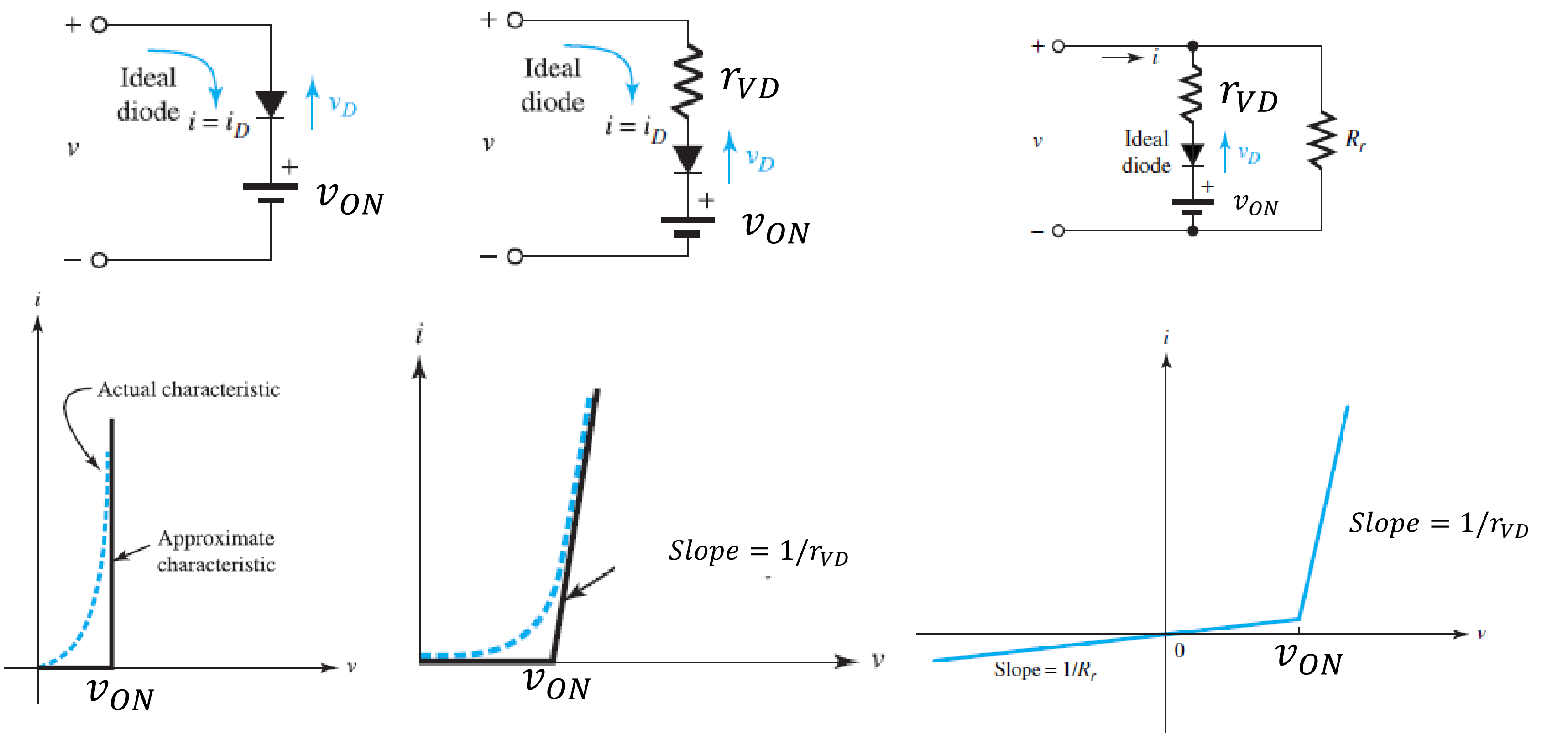
the *Boltzmann diode equation*

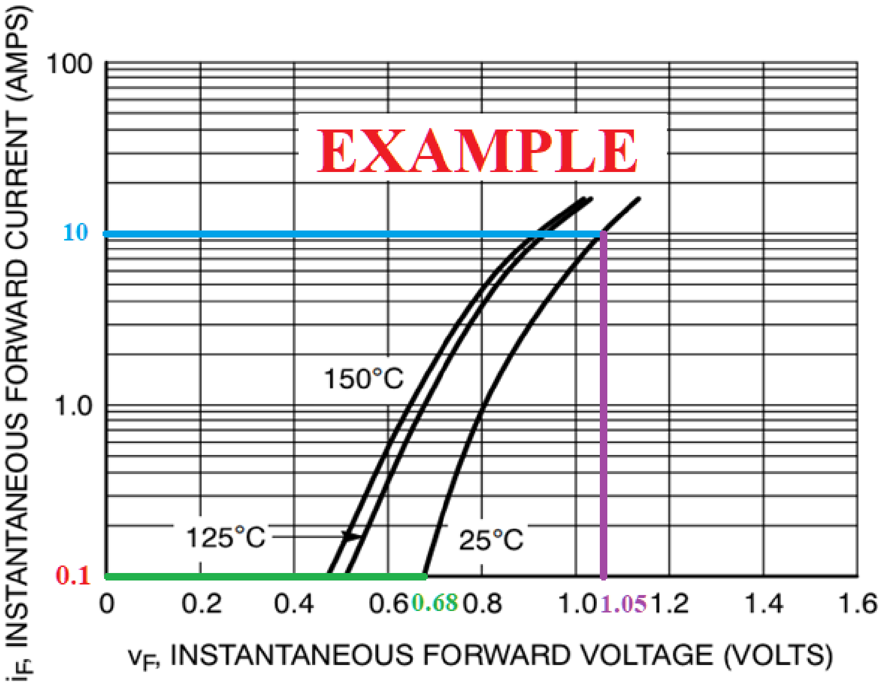
$$I = I_S(e^{V/\eta V_T} - 1)$$

$$V_T = \frac{kT}{q}$$

$$\eta = \begin{cases} 1, \text{for Si} \\ 2, \text{for Ge} \end{cases}$$

Forward-biased diode models





Maximum repetitive peak surge forward current

$$I_{fwd\_imp} = 10 \quad \text{(A)}$$

Diode forward bias voltage

$$V_{fwd\_max}(I_{fwd\_imp}) = 1.05 \quad \text{(V)}$$

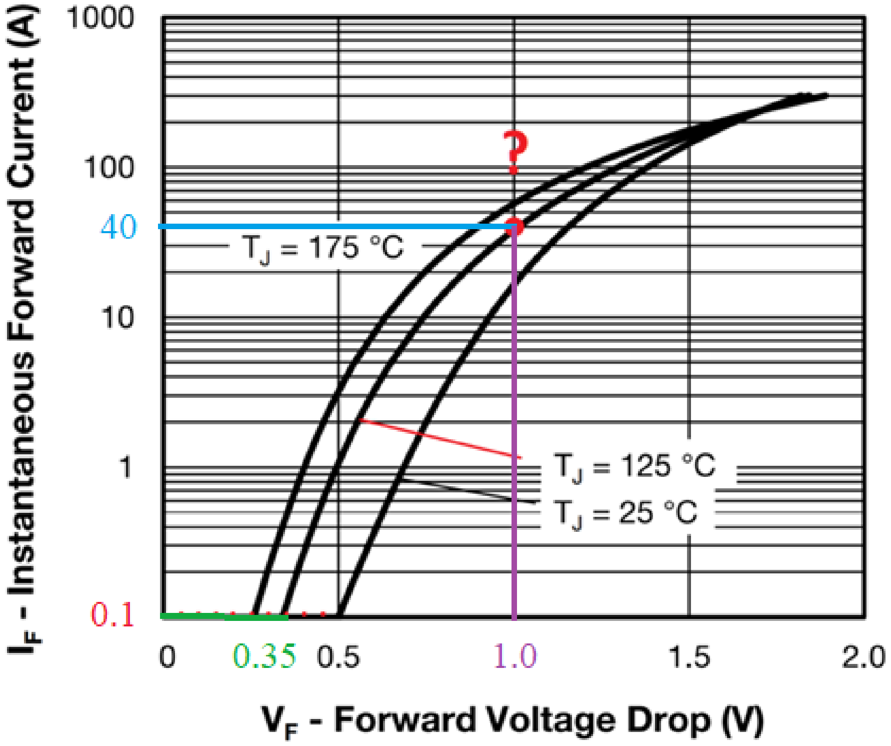
Diode threshold voltage:

$$v_{ON} = 0.68 \quad \text{(V)}$$

Diode active resistance:

$$r_{VD} = \frac{V_{fwd\_max} - v_{ON}}{I_{fwd_{imp}} - I_{fwd}(v_{ON})} = \quad (\Omega)$$

Diode active resistance



Maximum repetitive peak surge forward current

$$I_{fwd\_imp} = 40 \quad \text{(A)}$$

Diode forward bias voltage

$$V_{fwd\_max}\left(I_{fwd\_imp}\right) = 1.0 \quad \text{(V)}$$

Diode threshold voltage:

$$v_{ON} = 0.35 \quad \text{(V)}$$

Diode active resistance:

$$r_{VD} = \frac{V_{fwd\_max} - v_{ON}}{I_{fwd_{imp}} - I_{fwd}(v_{ON})} \quad (\Omega)$$

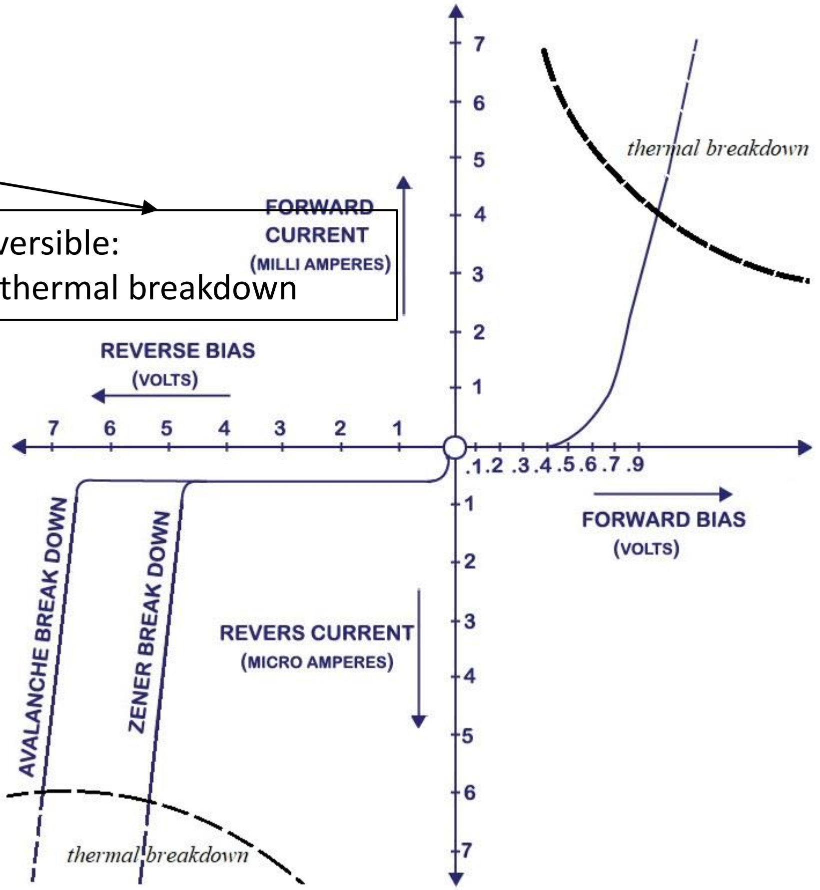
Diode breakdown

Diode breakdown

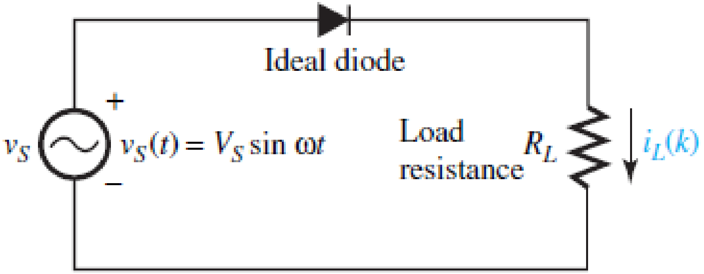
Reversible:
- *Zener breakdown* (at low voltages)
- *Avalanche breakdown* (at higher voltages)

Irreversible:
- thermal breakdown

Zener and Avalanche breakdown find application in stabilitrons.



Half-Wave Rectifier (HWR)



Source voltage $v_s(t)$

$$v_s(t) = V_s \cdot \sin(f \cdot 2\pi \cdot t) = V_s \cdot \sin(\omega \cdot t)$$

Voltage on the load resistance R_L

$$v_{R_L}(t) = \begin{cases} 0, & if \quad v_s(t) \le 0 \\ v_s(t), & if \quad v_s(t) > 0 \end{cases}$$

Load parameters:

$$V_{R_{L_{AVG}}} = \frac{V_s}{\pi} = \frac{\sqrt{2}V_{S_{RMS}}}{\pi} \approx 0.45 V_{S_{RMS}}$$

$$V_{R_{L\,RMS}} = \frac{V_s}{2} = \frac{V_{S_{RMS}}}{\sqrt{2}} \approx 0.707 V_{S_{RMS}}$$

Average load current

$$I_{L_{AVG}} = \frac{V_{R_{L_{AVG}}}}{R_L} = \frac{\sqrt{2}V_{S_{RMS}}}{\pi R_L} \approx 0.45 \frac{V_{S_{RMS}}}{R_L}$$

RMS load current through diode

$$I_{L_{RMS}} = \frac{V_s}{2R_L} = \frac{V_{S_{RMS}}}{\sqrt{2}R_L} \approx 0.707 \frac{V_{R_{L\,RMS}}}{R_L}$$

Diode parameters:

Average diode current

$$I_{VD_{AVG}} = I_{L_{AVG}} = \frac{\sqrt{2}V_{S_{RMS}}}{\pi R_L} \approx 0.45 \frac{V_{S_{RMS}}}{R_L}$$

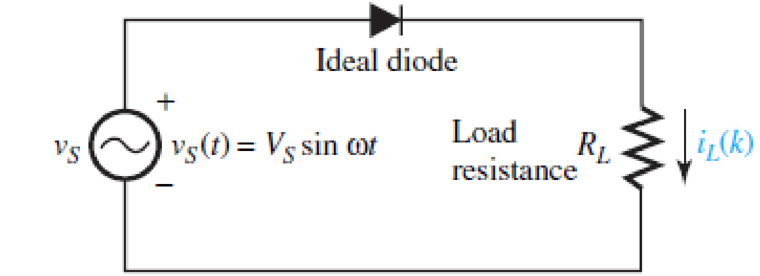
MAX diode current

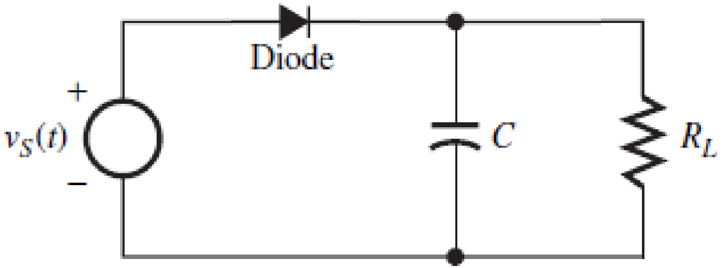
$$I_{VD_{max}} = \frac{V_s}{R_L}$$

MAX diode reverse voltage

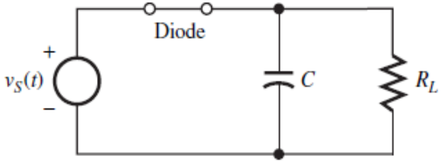
$$V_{VD_{max}} = V_s$$

Half-Wave Rectifier with DC filter capacitor

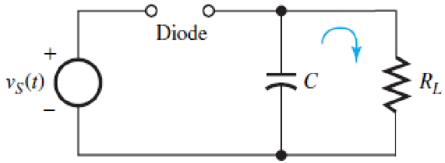




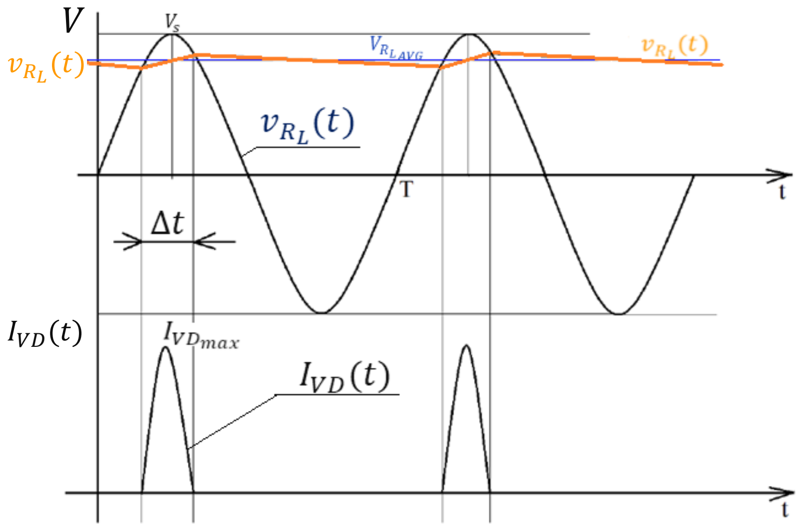
$0 \leq t \leq t_1$

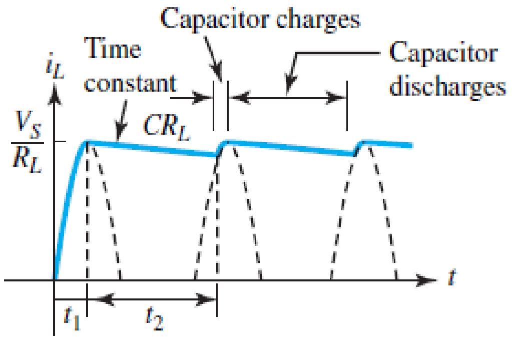


$0 \leq t \leq t_1$



$t_1 \leq t \leq t_2 + t_1$





Half-Wave Rectifier with DC filter capacitor

$$v_{R_L}(t) = V_{R_{LAVG}} + v_{R_{L\sim}}(t) \approx V_{R_L} \text{ =const}$$

Diode voltage:

$$v_{VD}(t) = v_s(t) - V_{R_{LAVG}}$$

Average diode current:

$$I_{LAVG} = I_{VD_{AVG}} = \frac{1}{T}\sqrt{\int_0^T I_{VD}(t)dt}$$

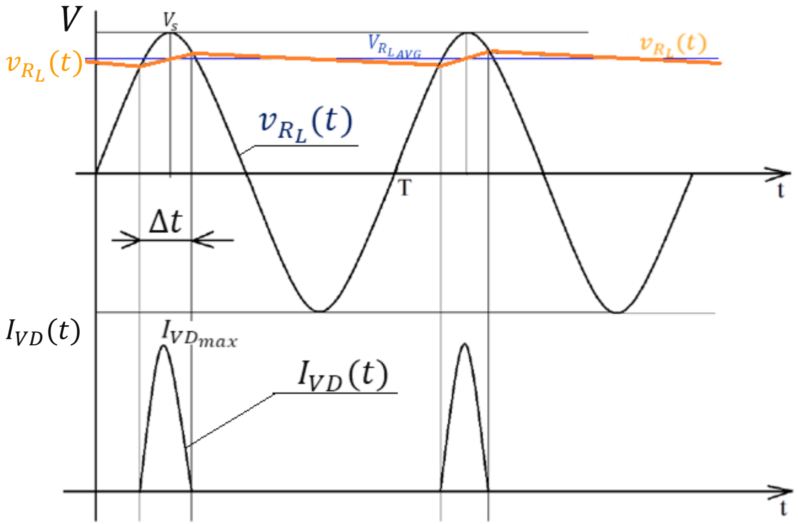
$$I_{LAVG} = \frac{1}{T}\sqrt{\int_{\frac{T}{4}-\theta/(2\cdot\omega)}^{\frac{T}{4}+\theta/(2\cdot\omega)} \frac{1}{r_{IN}}(V_s\cdot\sin(\omega\cdot t) - V_{R_{LAVG}}))dt} = \frac{V_{R_{LAVG}}}{\mathrm{R_L}}$$

Where

- $r_{IN} = r_{VD} + r_{V_S}$ – input resistance of the rectifier
- r_{VD} – diode resistance
- r_{V_S} – voltage source resistance
- $\theta = \omega\cdot\Delta t = \frac{2\pi}{T}\cdot\Delta t$ – angle of diode open state
- Δt – diode open state time interval

$$\frac{V_{R_{LAVG}}}{V_S} = \frac{\mathrm{R_L}}{\pi r_{IN}}(\sin\left(\frac{\theta}{2}\right) - \frac{V_{R_{LAVG}}}{V_S}\frac{\theta}{2})$$

$$V_{VD}\left(\frac{T}{4}\pm\frac{\theta}{2\cdot\omega}\right) = V_S\sin(\omega\left(\frac{T}{4}\pm\frac{\theta}{2\cdot\omega}\right)) - V_{R_{LAVG}} = 0 \Rightarrow V_{R_{LAVG}} = V_S(\omega\left(\frac{T}{4}\pm\frac{\theta}{2\cdot\omega}\right)) = V_S\sin\left(\frac{\pi}{2}\pm\frac{\theta}{2}\right)$$



Half-Wave Rectifier with DC filter capacitor

Average diode current:

$$I_{L_{AVG}} = \frac{1}{T}\sqrt{\int_{\frac{T}{4}-\theta/(2\cdot\omega)}^{\frac{T}{4}+\theta/(2\cdot\omega)} \frac{1}{r_{IN}}\left(V_s \cdot \sin(\omega\cdot t) - V_{R_{L_{AVG}}}\right)dt} = \frac{V_{R_{L_{AVG}}}}{\mathrm{R_L}}$$

Where

$r_{IN} = r_{VD} + r_{V_S}$ – input resistance of the rectifier

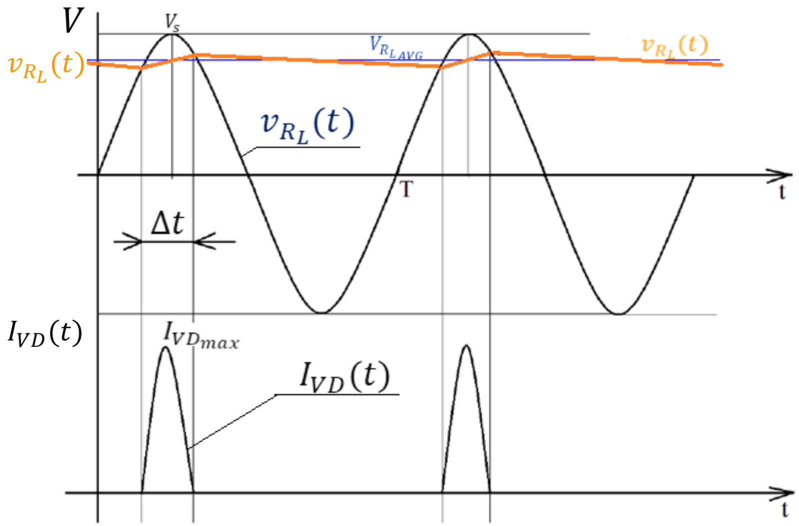
r_{VD} – diode resistance

r_{V_S} – voltage source resistance

$\theta = \omega \cdot \Delta t = \frac{2\pi}{T} \cdot \Delta t$ – angle of diode open state

Δt – diode open state time interval

$$\frac{V_{R_{L_{AVG}}}}{V_S} = \frac{\mathrm{R_L}}{\pi r_{IN}}\left(\sin\left(\frac{\theta}{2}\right) - \frac{V_{R_{L_{AVG}}}}{V_S}\frac{\theta}{2}\right)$$



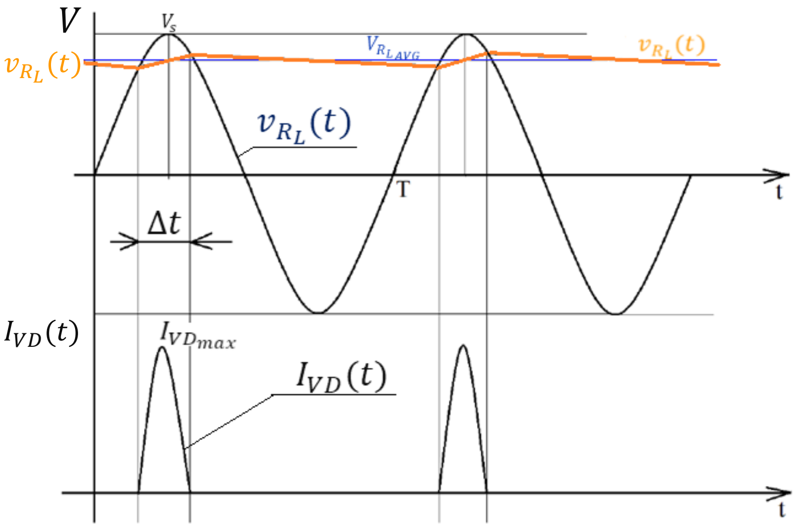
$$V_{VD}\left(\frac{T}{4} \pm \frac{\theta}{2\cdot\omega}\right) = V_S \sin\left(\omega\left(\frac{T}{4} \pm \frac{\theta}{2\cdot\omega}\right)\right) - V_{R_{L_{AVG}}} = 0 \Rightarrow V_{R_{L_{AVG}}} = V_S\left(\omega\left(\frac{T}{4} \pm \frac{\theta}{2\cdot\omega}\right)\right) = V_S \sin\left(\frac{\pi}{2} \pm \frac{\theta}{2}\right)$$

$$\frac{V_{R_{L_{AVG}}}}{V_S} = \cos\left(\frac{\theta}{2}\right) \Rightarrow \cos\left(\frac{\theta}{2}\right) = \frac{\mathrm{R_L}}{\pi r_{IN}}\left(\sin\left(\frac{\theta}{2}\right) - \cos\left(\frac{\theta}{2}\right)\cdot\frac{\theta}{2}\right) \Rightarrow \frac{r_{IN}}{\mathrm{R_L}} = \frac{1}{\pi}\left(\tan\left(\frac{\theta}{2}\right) - \frac{\theta}{2}\right)$$

Half-Wave Rectifier with DC filter capacitor

From $\frac{r_{IN}}{\mathrm{R_L}} = \frac{1}{\pi}\left(\tan\left(\frac{\theta}{2}\right) - \frac{\theta}{2}\right)$
angle of diode open state θ can be evaluated:

$$\tan\left(\frac{\theta}{2}\right) \approx \frac{\theta}{2} + \frac{1}{3}\left(\frac{\theta}{2}\right)^3 \Rightarrow \theta = 2 \cdot \sqrt[3]{3\pi \frac{r_{IN}}{\mathrm{R_L}}}$$



Average load voltage: $V_{R_{L AVG}} = V_S \cos\left(\frac{\theta}{2}\right)$

Average load (diode) current: $I_{VD} = \frac{V_S}{\mathrm{R_L}} \cos\left(\frac{\theta}{2}\right)$

Peak (repetitive) diode current: $I_{VDmax} = \frac{V_S - V_{R_{L AVG}}}{r_{IN}}$

Peak (turn on) diode current: $I_{VDON} = \frac{V_S}{r_{IN}}$

Diode reverse voltage: $V_{VDmax} = V_S + V_{R_{L AVG}} \approx 2 \cdot V_S$

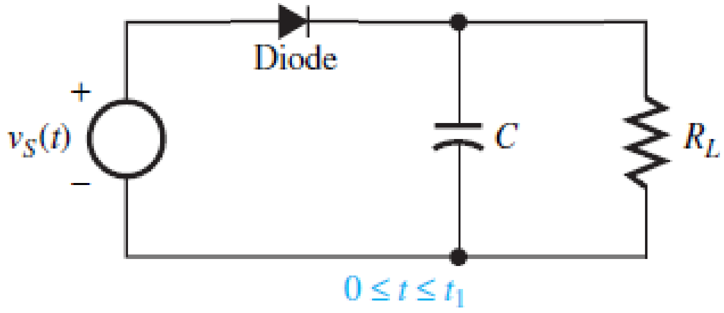
Half-Wave Rectifier with DC filter capacitor

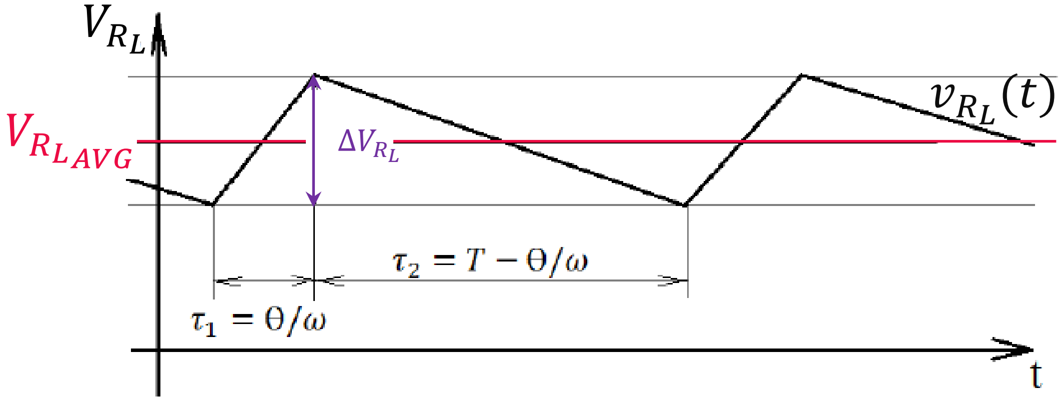
From equation of capacitor charge on the interval of $\tau_1 < t < \tau_2 = T - \frac{\theta}{\omega}$

$$\Delta Q = C \cdot \Delta V_{R_L} = I_{L_{AVG}}\left(T - \frac{\theta}{\omega}\right) \quad \text{(C)}$$

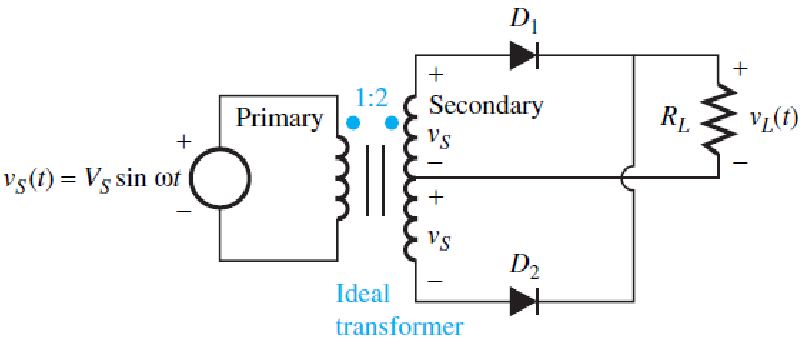
Power filter capacitor evaluation to provide required ripple factor

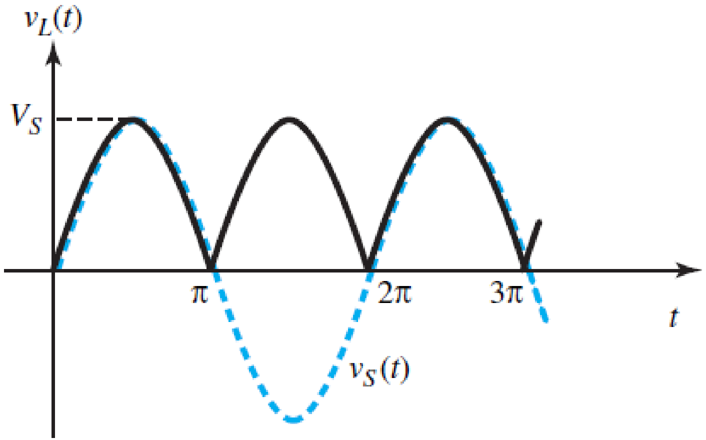
$$C = \frac{I_{L_{AVG}}}{2\pi f \cdot \Delta V_{R_L}}(2\pi - \theta) = \frac{I_{L_{AVG}}}{\omega \cdot \Delta V_{R_L}}(2\pi - \theta) \quad \text{(F)}$$

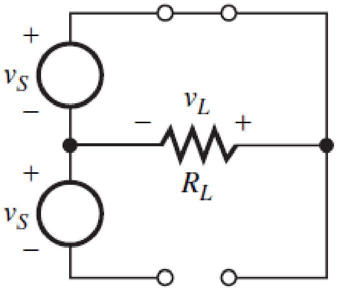




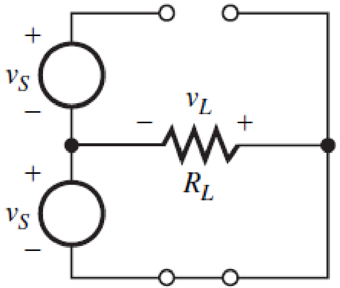
Center-Tap Full Wave Rectifier



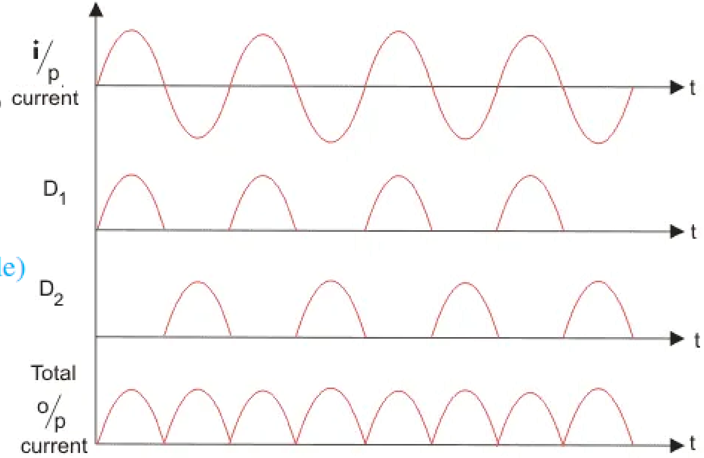




$v_S > 0$ (positive half-cycle)



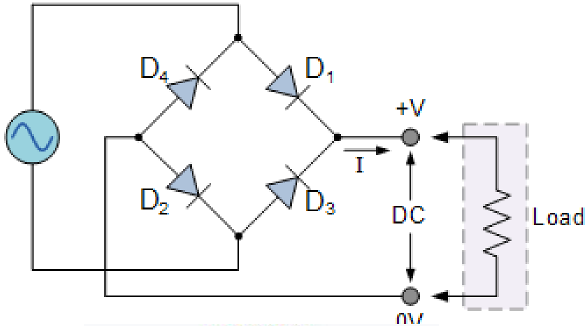
$v_S < 0$ (negative half-cycle)

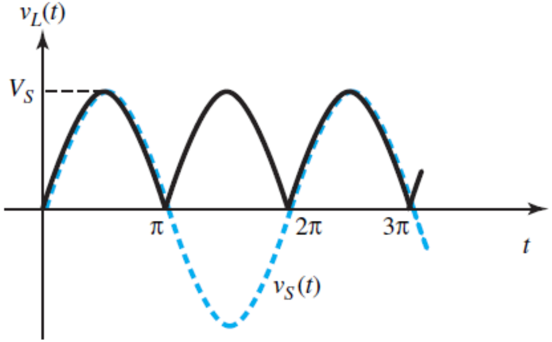


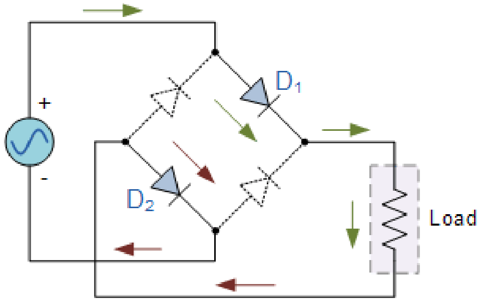
Vladimir Mitkevich

BORN: 22/06/1872 (03. 08. 1872)
in MINSK, (Russian Empire,
now it's the capital of BELARUS)
Death: 01/06/1951
Moscow, Soviet Russia
Worked in Peter the Great
St.Petersburg Polytechnic University

Full Wave Bridge Rectifier





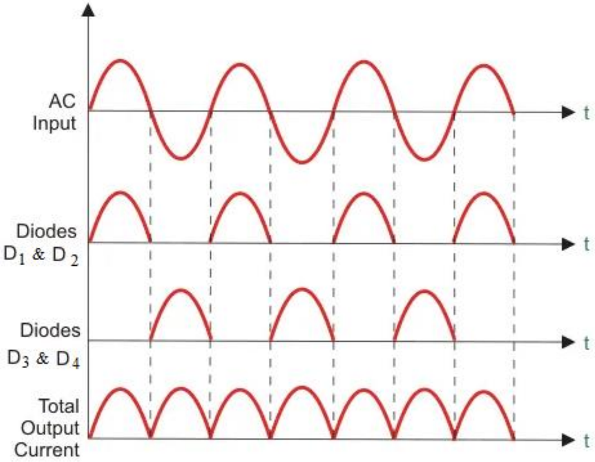


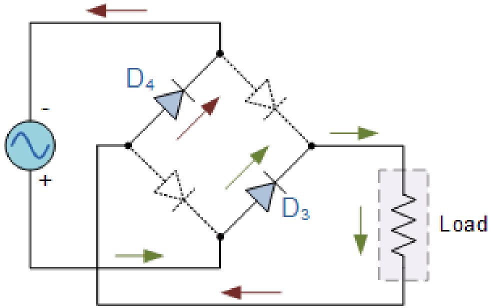
The Positive Half-cycle

Leo Graetz

Leo Graetz, painted by Franz von Stuck (1906)

Born	26 September 1856 Breslau, Prussia
Died	12 November 1941 (aged 85) Munich, Nazi Germany
Known for	Graetz number, Diode bridge





The Negative Half-cycle

Full-Wave rectifiers (without C-filter)

- **Average load voltage:** $$V_{R_{L\,AVG}} = \begin{cases} \frac{V_S}{\pi}, & \text{for } \textbf{HWR} \text{ schemes} \\ \frac{2 \cdot V_S}{\pi}, & \text{for } \textbf{FBR} \text{ or } \textbf{CTR} \text{ schemes} \end{cases} \quad \text{(V)}$$
- **RMS load voltage:** $$V_{R_{L\,RMS}} = \begin{cases} \frac{V_S}{2}, & \text{for } \textbf{HWR} \text{ schemes} \\ \frac{V_S}{\sqrt{2}}, & \text{for } \textbf{FBR} \text{ or } \textbf{CTR} \text{ schemes} \end{cases} \quad \text{(V)}$$
- **Max peak diode reverse voltage:** $$V_{VD_{max}} = V_S \quad \text{(V)}$$
- **Average load current:** $$I_{L_{AVG}} = \frac{V_{R_{L\,AVG}}}{R_L} = \begin{cases} \frac{V_S}{\pi R_L}, & \text{for } \textbf{HWR} \text{ schemes} \\ \frac{2 \cdot V_S}{\pi R_L}, & \text{for } \textbf{FBR} \text{ or } \textbf{CTR} \text{ schemes} \end{cases} \quad \text{(A)}$$
- **RMS load current:** $$I_{L_{RMS}} = \frac{V_{R_{L\,RMS}}}{R_L} = \begin{cases} \frac{V_S}{2R_L}, & \text{for } \textbf{HWR} \text{ schemes} \\ \frac{V_S}{\sqrt{2}R_L}, & \text{for } \textbf{FBR} \text{ or } \textbf{CTR} \text{ schemes} \end{cases} \quad \text{(A)}$$

Full-Wave rectifiers (without C-filter)

iTMO

- **Average diode rectified output current:**

$$I_{VD} = \begin{cases} I_{L_{AVG}}, & \text{for } \mathbf{HWR} \text{ schemes} \\ \dfrac{I_{L_{AVG}}}{2}, & \text{for } \mathbf{FBR} \text{ or } \mathbf{CTR} \text{ schemes} \end{cases} \quad \text{(A)}$$

- **Peak repetitive forward output current:**

$$I_{VD_{max}} = \begin{cases} \dfrac{V_S}{R_L}, & \text{for } \mathbf{HWR} \text{ schemes} \\ \dfrac{V_S}{2R_L}, & \text{for } \mathbf{FBR} \text{ or } \mathbf{CTR} \text{ schemes} \end{cases} \quad \text{(A)}$$

- **Voltage ripple factor:** $K_p = \sqrt{\left(\dfrac{V_{R_{L_{RMS}}}}{V_{R_{L_{AVG}}}}\right)^2 - 1} = \begin{cases} \sqrt{\left(\dfrac{\pi}{2}\right)^2 - 1} \approx 1.21, & \text{for } \mathbf{HWR} \text{ schemes} \\ \sqrt{\left(\dfrac{\pi}{2\cdot\sqrt{2}}\right)^2 - 1} \approx 0.48 & \text{for } \mathbf{FBR} \text{ or } \mathbf{CTR} \text{ schemes} \end{cases}$

- **Voltage ripple evaluated for the rectifier scheme:**

$$\Delta V_{R_L} = 2 \cdot K_p \cdot V_{R_{L_{AVG}}} = \begin{cases} \dfrac{2\cdot V_S}{\pi}\sqrt{\left(\dfrac{\pi}{2}\right)^2 - 1} \approx \dfrac{2.48\cdot V_S}{\pi} \approx 0.79 V_S, & \text{for } \mathbf{HWR} \text{ schemes} \\ \dfrac{4\cdot V_S}{\pi}\sqrt{\left(\dfrac{\pi}{2\cdot\sqrt{2}}\right)^2 - 1} \approx \dfrac{1.92\cdot V_S}{\pi} \approx 0.61 V_S & \text{for } \mathbf{FBR} \text{ or } \mathbf{CTR} \text{ schemes} \end{cases} \quad \text{(V)}$$

Full-Wave rectifiers (with C-filter)

- **Source output resistance (overcurrent protection):** $r_{on} = \frac{V_S}{I_{FSM}}$ (Ω)
- **Input rectifier resistance:** $r_{IN} = \begin{cases} r_{vd} + r_{V_S}, & \text{for HWR } or \text{ CTR schemes} \\ 2 \cdot r_{vd} + r_{V_S}, & \text{for FBR schemes} \end{cases}$ (Ω)
- **Diode opening state angle:** $\theta = \begin{cases} 2 \cdot \sqrt[3]{3 \cdot \pi \cdot \frac{r_{IN}}{R_L}}, & \text{for HWR schemes} \\ 2 \cdot \sqrt[3]{\frac{3}{2} \cdot \pi \cdot \frac{r_{IN}}{R_L}}, & \text{for FBR or CTR schemes} \end{cases}$ (rad)
- **Average load voltage** $V_{R_{L_{AVG}}} = V_S \cdot \cos\left(\frac{\theta}{2}\right) = \begin{cases} V_S \cdot \cos\left(\sqrt[3]{3 \cdot \pi \cdot \frac{r_{IN}}{R_L}}\right), & \text{for HWR schemes} \\ V_S \cdot \cos\left(\sqrt[3]{\frac{3}{2} \cdot \pi \cdot \frac{r_{IN}}{R_L}}\right), & \text{for FBR or CTR schemes} \end{cases}$ (V)
- **Average load current:** $I_{L_{AVG}} = \begin{cases} \frac{1}{\pi \cdot r_{IN}} \left(V_S \cdot \sin\left(\frac{\theta}{2}\right) - V_{R_{L_{AVG}}} \cdot \frac{\theta}{2}\right), & \text{for HWR schemes} \\ \frac{2}{\pi \cdot r_{IN}} \left(V_S \cdot \sin\left(\frac{\theta}{2}\right) - V_{R_{L_{AVG}}} \cdot \frac{\theta}{2}\right), & \text{for FBR or CTR schemes} \end{cases}$ (A)

Full-Wave rectifiers (with C-filter)

- **Average diode current:**

$$I_{VD} = \begin{cases} \frac{V_S}{R_L} \cdot \cos\left(\frac{\theta}{2}\right) = \frac{V_S}{R_L} \cdot \cos\left(\sqrt[3]{3 \cdot \pi \cdot \frac{r_{IN}}{R_L}}\right), & \text{for HWR schemes} \\ \frac{V_S}{2 \cdot R_L} \cdot \cos\left(\frac{\theta}{2}\right) = \frac{V_S}{2 \cdot R_L} \cdot \cos\left(\sqrt[3]{\frac{3}{2} \cdot \pi \cdot \frac{r_{IN}}{R_L}}\right), & \text{for FBR or CTR schemes} \end{cases} \quad \text{(A)}$$

- **Maximum repetitive rectifier scheme diode current:**

$$I_{VD_{max}} = \frac{V_S - V_{R_{L_{AVG}}}}{r_{IN}} \quad \text{(A)}$$

- **Starting (Non-repetitive) maximum peak surge diode current in rectifier scheme:** $I_{VD_{ON}} = \frac{V_S}{r_{IN}}$ (A)

- **Peak repetitive reverse voltage:**

$$V_{VD_{max}} = \begin{cases} V_S + V_{R_{L_{AVG}}}, & \text{for HWR or CTRschemes} \\ \frac{V_S + V_{R_{L_{AVG}}}}{2}, & \text{for FBR schemes} \end{cases} \quad \text{(V)}$$

- **Capacitance evaluation:**

$$C = \begin{cases} \frac{I_{L_{AVG}}}{2\pi f \cdot \Delta V_{R_L}} (2\pi - \theta), & \text{for HWR schemes} \\ \frac{I_{L_{AVG}}}{2\pi f \cdot \Delta V_{R_L}} (\pi - \theta), & \text{for FBR or CTR schemes} \end{cases} \quad \text{(F)}$$

- **Voltage ripple:**

$$\Delta V_{R_L} = \begin{cases} \frac{I_{L_{AVG}}}{2\pi f \cdot C} (2\pi - \theta), & \text{for HWR schemes} \\ \frac{I_{L_{AVG}}}{2\pi f \cdot C} (\pi - \theta), & \text{for FBR or CTR schemes} \end{cases} \quad \text{(V)}$$

- **Voltage ripple factor**

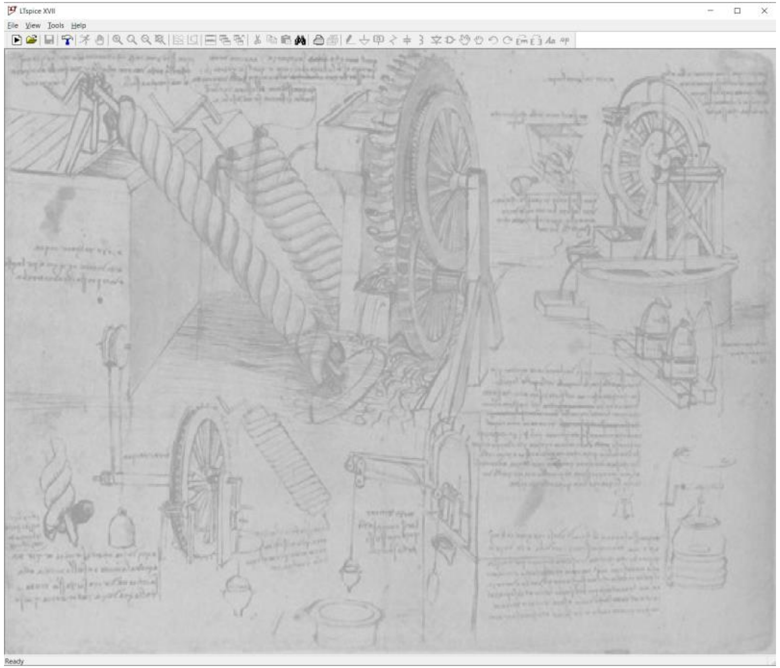
$$K_p = \frac{\Delta V_{R_L}}{2 V_{R_{L_{AVG}}}}$$

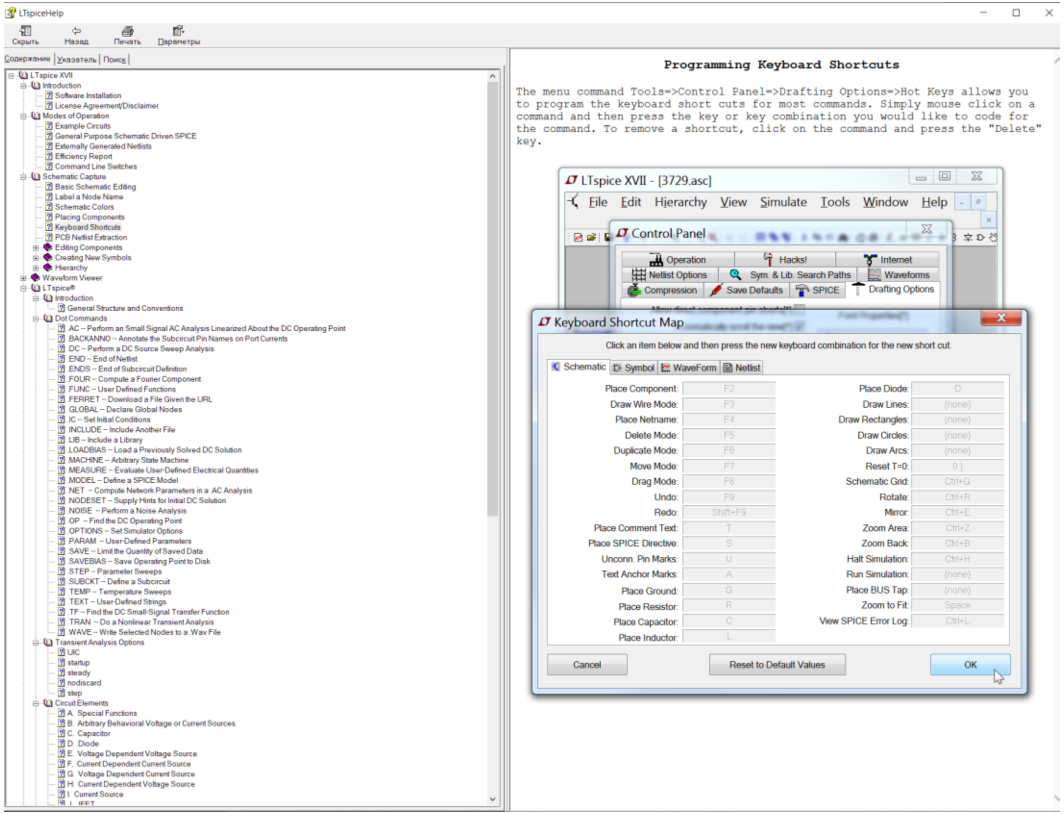
Evaluations

iTMO

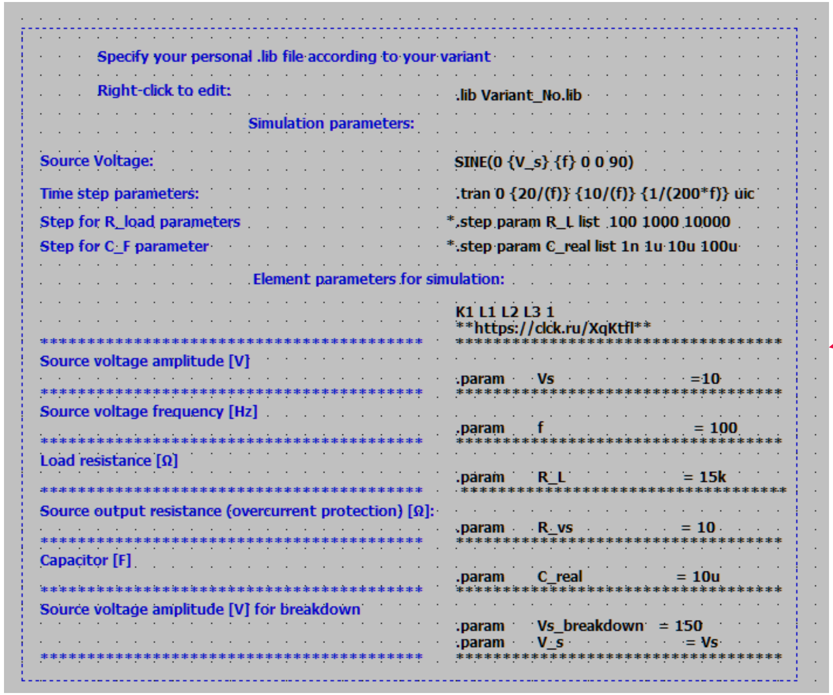
	$I_{VD_{AVG}}$	$I_{VD_{max}}$	$V_{VD_{max}}$	r_{IN}
Half - Wave rectifier (HWR)	$= I_{L_{AVG}}$	$\approx 7I_{L_{AVG}}$	$= V_S \cdot 2 \approx 3V_{R_{L_{AVG}}}$	$= r_{VD} + r_{V_s}$
Central Tap Rectifier (CTR)	$= \frac{I_{L_{AVG}}}{2}$	$\approx 3.5I_{L_{AVG}}$	$= V_S \cdot 2 \approx 3V_{R_{L_{AVG}}}$	$= r_{VD} + r_{V_s}$
Full bridge (Graetz) rectifier (FBR)	$= \frac{I_{L_{AVG}}}{2}$	$\approx 3.5I_{L_{AVG}}$	$= V_S \approx 1.5V_{R_{L_{AVG}}}$	$=2r_{VD} + r_{V_s}$

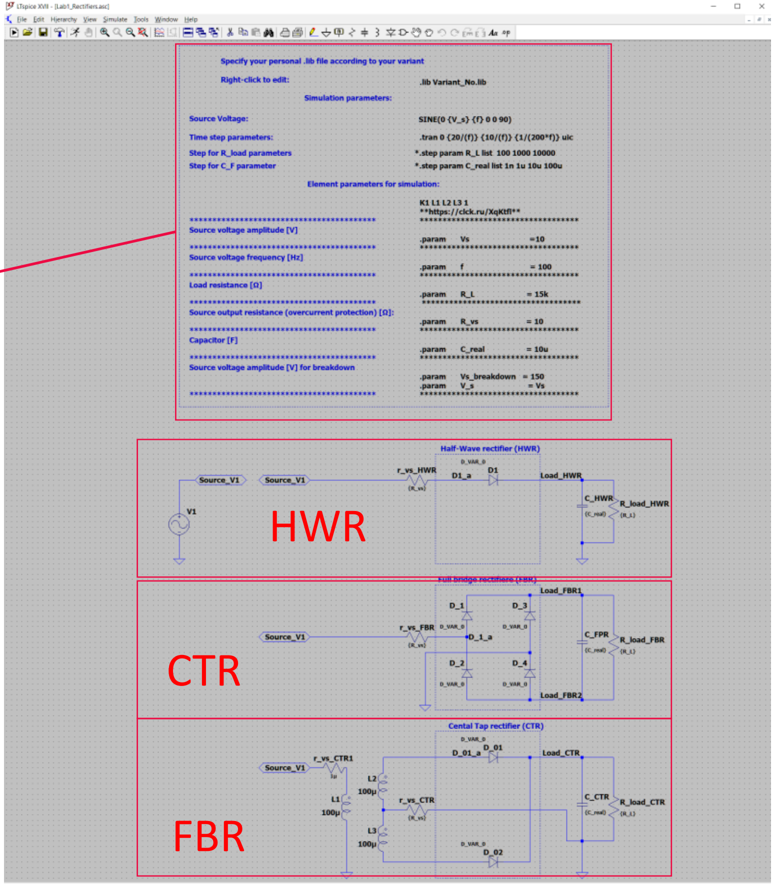
Step One: LT Spice XVII start





Step Two: Lab1_Rectifiers.asc



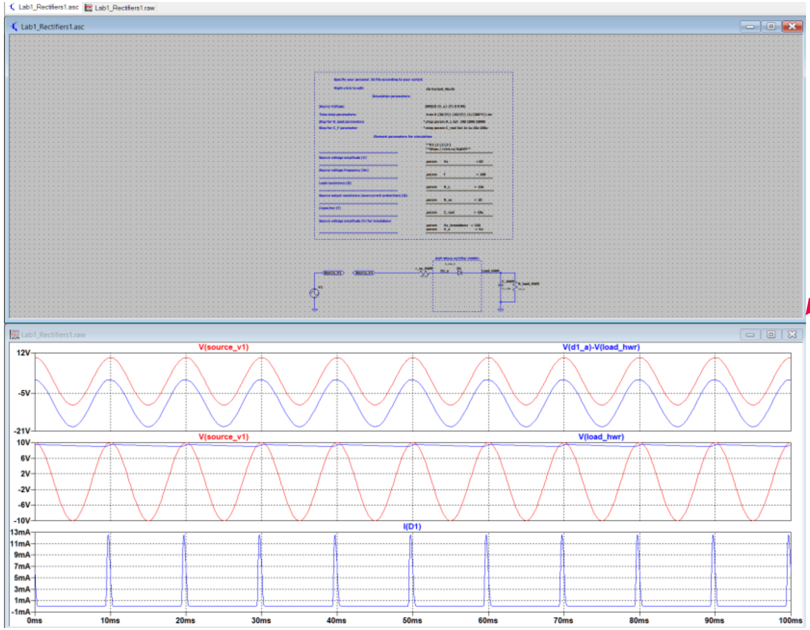


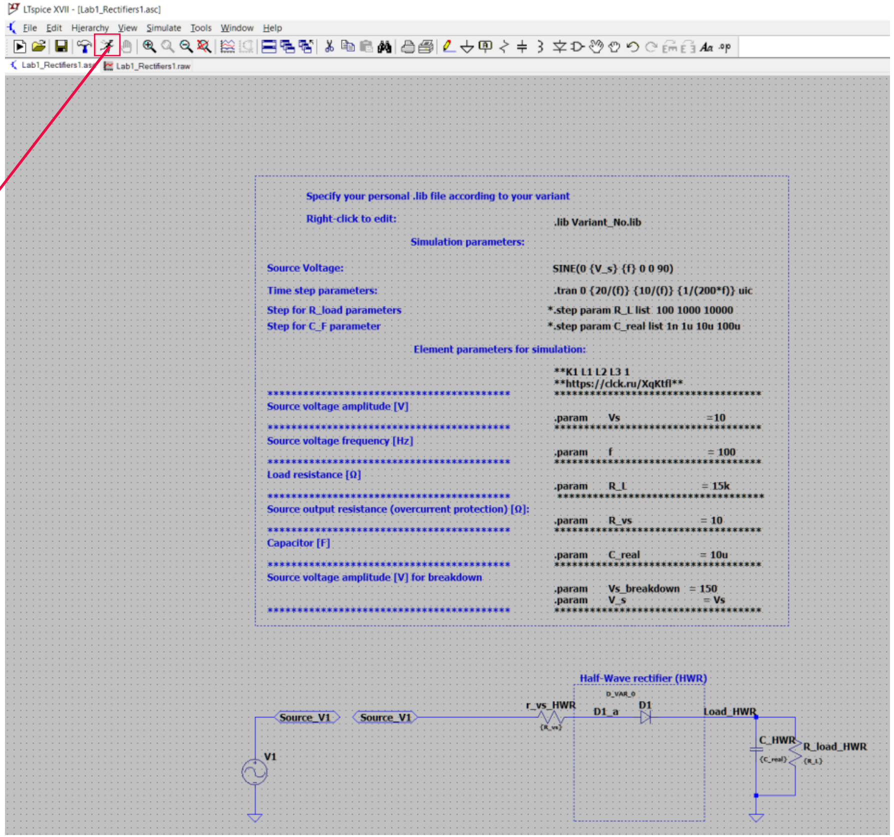
Step Three: Variant data

```
Specify your personal .lib file according to your variant
Right-click to edit:                                   .lib Variant_No.lib
                        Simulation parameters:
Source Voltage:                                  SINE(0 {V_s} {f} 0 0 90)
Time step parameters:                            .tran 0 {20/(f)} {10/(f)} {1/(200*f)} uic
Step for R_load parameters                       *.step param R_L list 100 1000 10000
Step for C_F parameter                           *.step param C_real list 1n 1u 10u 100u
                        Element parameters for simulation:
                                                 K1 L1 L2 L3 1
                                                 **https://clck.ru/XqKtfl**
*****************************************        ***********************************
Source voltage amplitude [V]
                                                 .param    Vs              =10
*****************************************        ***********************************
Source voltage frequency [Hz]
                                                 .param    f               = 100
*****************************************        ***********************************
Load resistance [Ω]
                                                 .param    R_L             = 15k
*****************************************        ***********************************
Source output resistance (overcurrent protection) [Ω]:
                                                 .param    R_vs            = 10
*****************************************        ***********************************
Capacitor [F]
                                                 .param    C_real          = 10u
*****************************************        ***********************************
Source voltage amplitude [V] for breakdown
                                                 .param    Vs_breakdown  = 150
                                                 .param    V_s             = Vs
*****************************************        ***********************************
```

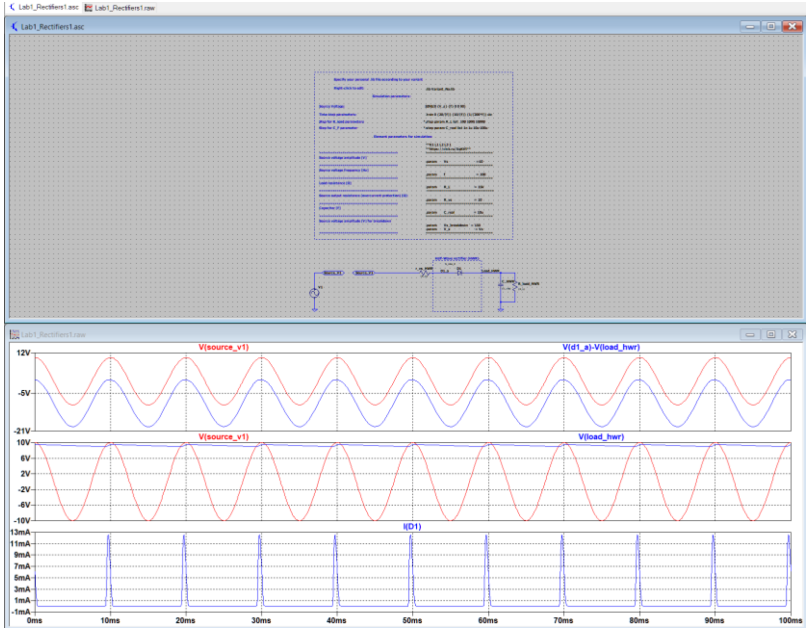
Variant #	Rectifier scheme	Source voltage amplitude, [V]	Load resistance, [Ω]	Desired DC voltage ripple factor	Source voltage frequency, [Hz]
	HWR-half-wave rectifier, **CTR**-central tap rectifier, **FBR** - full bridge rectifier	V_s	R_L	K_P	f

Step Four: Simulation





Step Five: Results



1. Work purpose: to study parameters of semiconductor elements and basis of the semiconductor device design

Goals:
1) Design rectifier model on the basis of diode «diode name»
2) Simulate rectifier scheme and analyze dependencies of DC voltage ripple from load and filter capacitor values variation
3) Simulate overvoltage and overcurrent states (optional)

2. Starting data

2.1.1. Parameters of the voltage source:

- One-phase sine voltage source
- Rectifier scheme: Half-Wave Rectifier (HWR) /Central tap rectifier (CTR) /Full -Bridge rectifier (FBR)
- Source voltage amplitude

$V_s =$ (V)

- Source voltage frequency

f= (Hz)

2.1.2. Diode: (copy the 1stand the second line of .lib file of your variant)

2.1.3. Required parameters of DC output:

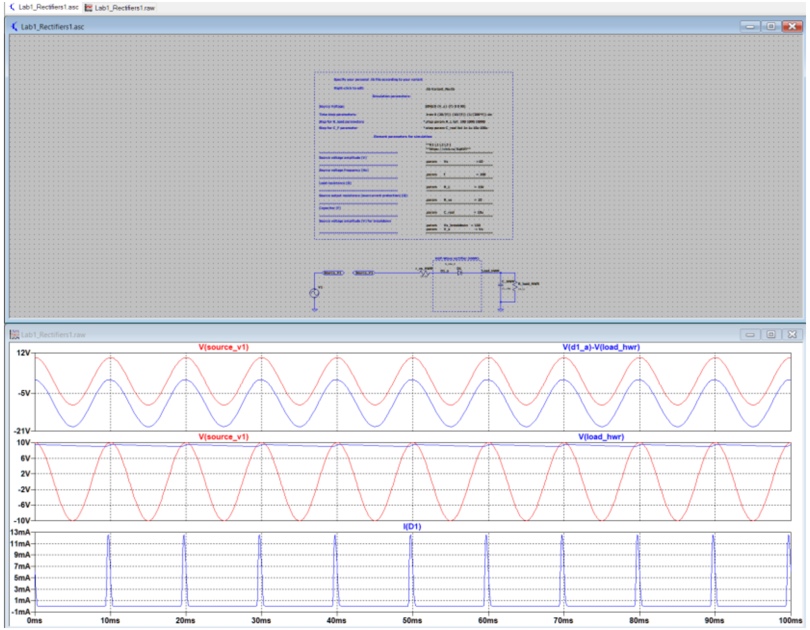
- Load resistance:

$R_L = R_{LOAD\_HWR/CTR/FBR} =$ (V)

- Desired DC voltage ripple factor:

$K_n =$.

Step Five: Results



3. Simulation report

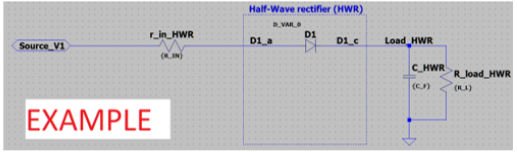


Fig. 3.1 – Rectifier scheme model

3.1.1. Filter parameters:

— C_{real} = 470____________________(uF)

3.1.2. Load parameters:

— $R_L = R_{LOAD\_HWR} =$ 667____________________(Ω)

— $V_{R_{L_{AVG}}}$= 23.676V____________________(V)

— $V_{R_{L_{RMS}}}$= 23.679V____________________(V)

— $K_p = K_p = \frac{\Delta V_{R_L}}{2V_{R_{L\,AVG}}} =$ ____________________

— $I_{VD_{ON}} =$ ____________________(A)

— $I_{VD_{max}} =$ ____________________(A)

— $\Delta V_{R_L} =$ ____________________(V)

3.2. Simulation results

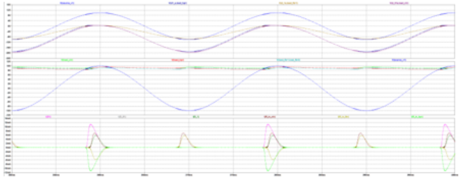
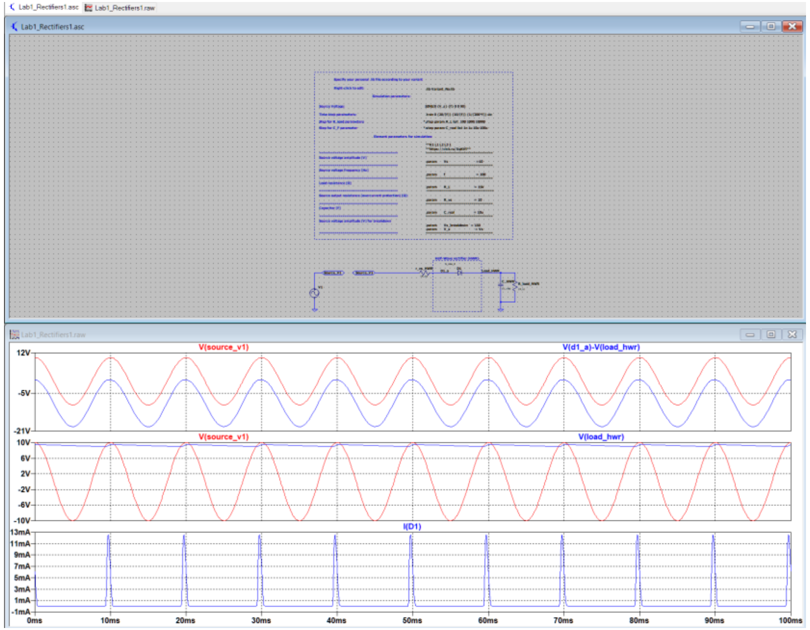


Fig 3.2 – Simulation results

Step Five: Results

iTMO



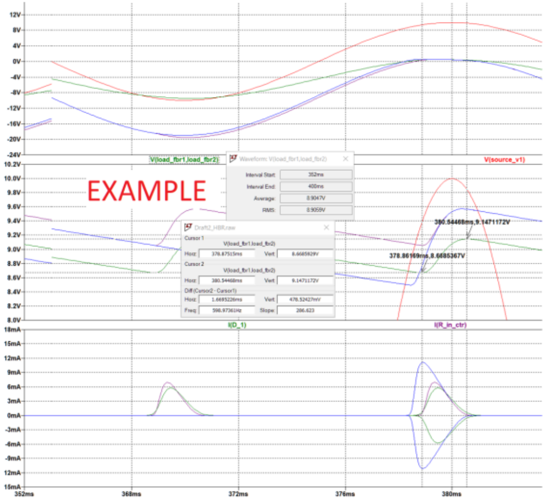
3.2.1. Ripple factor:

Required:

— K_p = ____________________

Simulated with 0.8 C_{real}

— K_{P_EXP} = ____________________



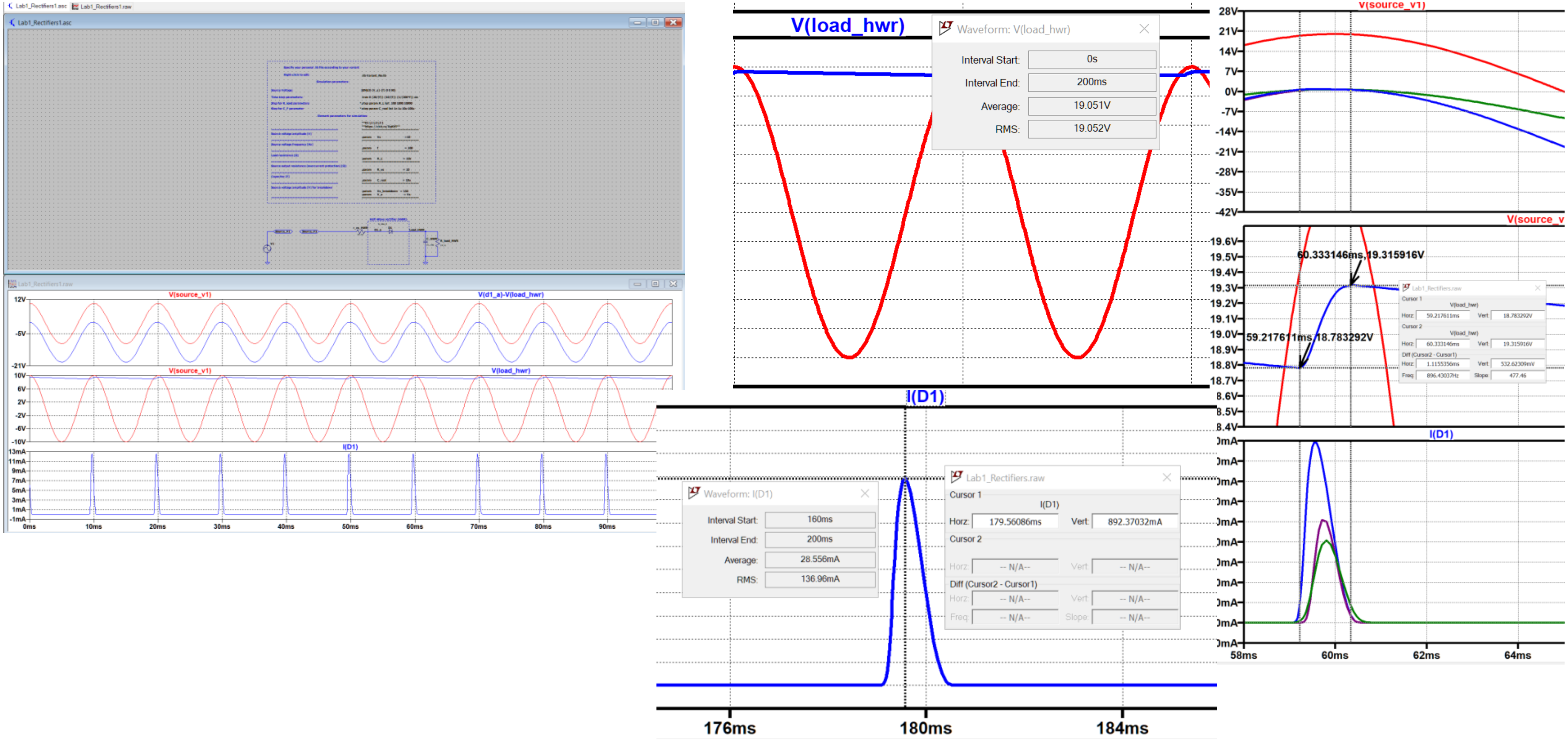
b) Full-bridge rectifier

Fig 3.3 –Voltage ripple analysis

To define Average and RMS values use CTRL+left click mouse button on the signal name. **Use 2-3 Voltage periods in the end of simulation interval**

Right-click with mouse on the signal name gives access to the signal cursor

Step Five: Results



Theta issues

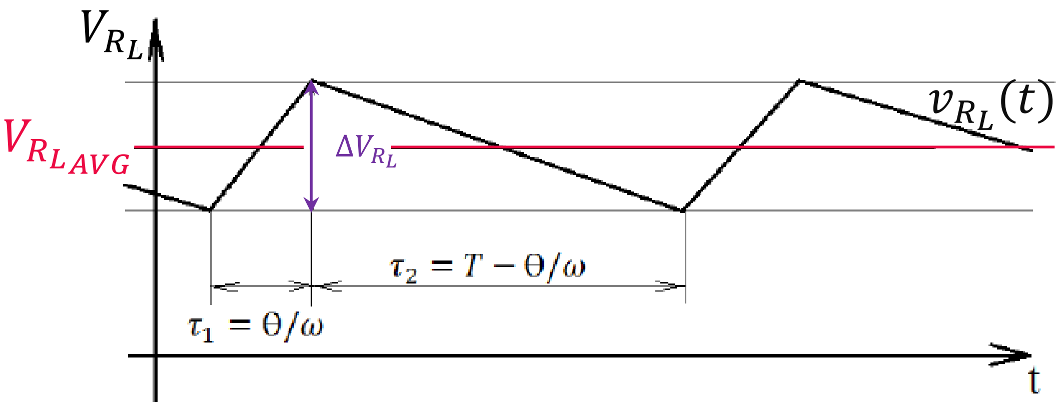
From equation of capacitor charge on the interval of $\tau_1 < t < \tau_2 = T - \frac{\theta}{\omega}$

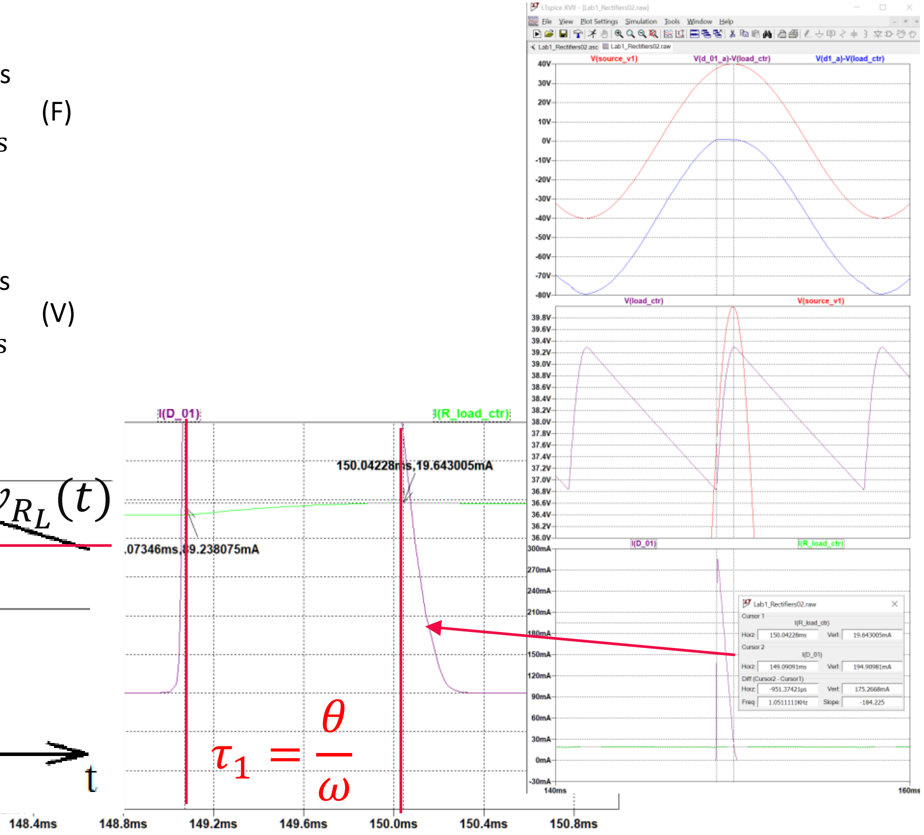
Capacitance evaluation:

$$C = \begin{cases} \frac{I_{L_{AVG}}}{2\pi f \cdot \Delta V_{R_L}}(2\pi - \theta), & \text{for HWR schemes} \\ \frac{I_{L_{AVG}}}{2\pi f \cdot \Delta V_{R_L}}(\pi - \theta), & \text{for FBR or CTR schemes} \end{cases} \quad \text{(F)}$$

Voltage ripple:

$$\Delta V_{R_L} = \begin{cases} \frac{I_{L_{AVG}}}{2\pi f \cdot C}(2\pi - \theta), & \text{for HWR schemes} \\ \frac{I_{L_{AVG}}}{2\pi f \cdot C}(\pi - \theta), & \text{for FBR or CTR schemes} \end{cases} \quad \text{(V)}$$





Theta issues

From equation of capacitor charge on the interval of $\tau_1 < t < \tau_2 = T - \dfrac{\theta}{\omega}$

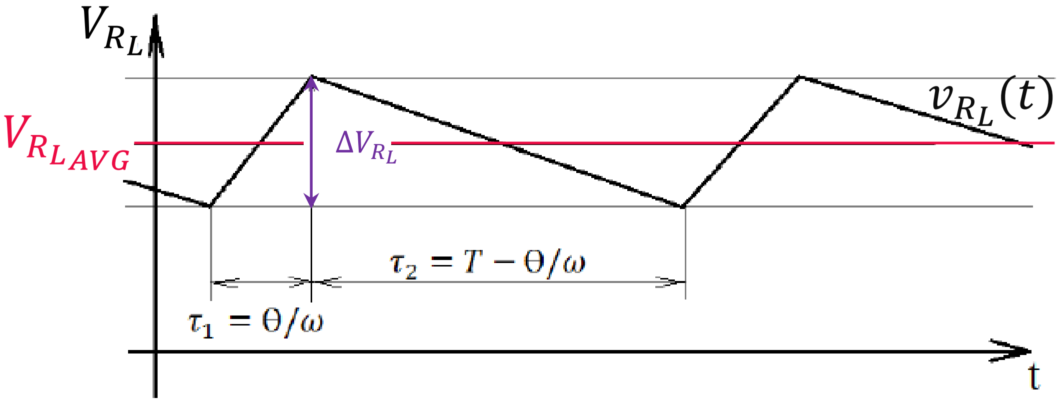
Capacitance evaluation:

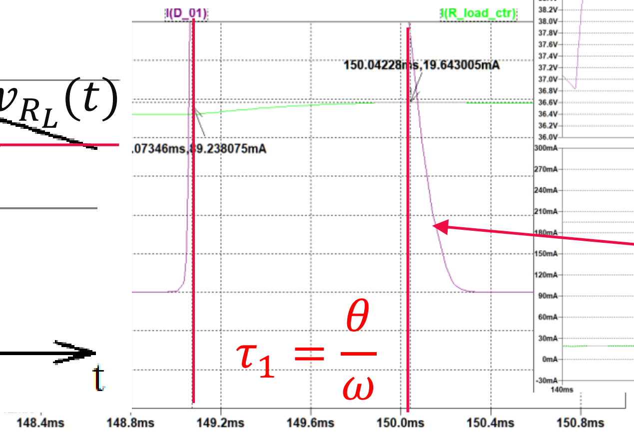
$$C = \begin{cases} \dfrac{I_{L_{AVG}}}{2\pi f \cdot \Delta V_{R_L}} (2\pi - \theta)\,, & \text{for } \textbf{HWR} \text{ schemes} \\ \dfrac{I_{L_{AVG}}}{2\pi f \cdot \Delta V_{R_L}} (\pi - \theta), & \text{for } \textbf{FBR} \text{ or } \textbf{CTR} \text{ schemes} \end{cases} \qquad \text{(F)}$$

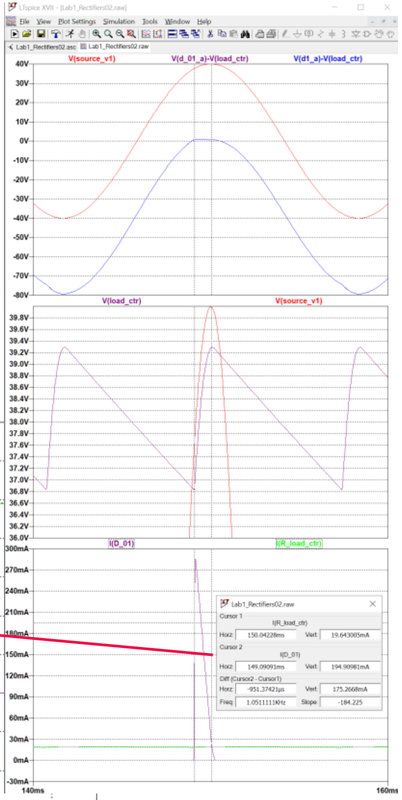
Voltage ripple:

$$\Delta V_{R_L} = \begin{cases} \dfrac{I_{L_{AVG}}}{2\pi f \cdot C} (2\pi - \theta), & \text{for } \textbf{HWR} \text{ schemes} \\ \dfrac{I_{L_{AVG}}}{2\pi f \cdot C} (\pi - \theta), & \text{for } \textbf{FBR} \text{ or } \textbf{CTR} \text{ schemes} \end{cases} \qquad \text{(V)}$$

If currents are less 1A it is better to use open –state current value al least 100mA to determine theta from simulation







Step Five: Results

• 3.2.2. Voltage ripple from simulation results

$$V_{R_{L AVG} exp} = \quad \text{(V)}$$

$$V_{R_{L RMS} exp} = \quad \text{(V)}$$

$$V_{R_{L max}} = \quad \text{(V)}$$

$$V_{R_{L min}} = \quad \text{(V)}$$

$$\Delta V_{R_L exp} = V_{R_{L max}} - V_{R_{L min}} = \quad \text{(V)}$$

• 3.2.3. Ripple factor

$$K_{P exp} = \frac{\Delta V_{R_L exp}}{2 \cdot V_{R_{L AVG} exp}} =$$

$$K_{pRMS} \approx \sqrt{\left(\frac{\Delta V_{R_L}/2\sqrt{3}}{V_{R_{L AVG}}}\right)^2} = \sqrt{\left(\frac{V_{R_L\_RMS}}{V_{R_{L AVG}}}\right)^2 - 1}$$

• 3.2.4. Diode opening state angle:

$$\tau_1 = \quad \text{(s)}$$

$$\theta_{exp} = \tau_1 \cdot f \cdot 2\pi = \frac{\tau_1}{T} \cdot 2\pi = \quad \text{(rad)}$$

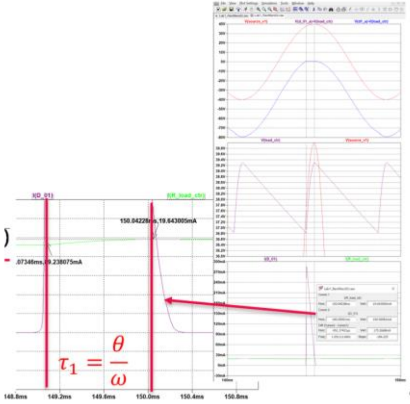


Fig 3.4 – θ_{exp} angle definition from simulation results
(It is recommended to consider diode open state at current level 0.05-0.1A or determine theta on the capacitor charging interval)

LABORATORY WORK REPORT №1 6

3.2.6. Starting (Non-repetitive) maximum peak surge diode current in rectifier scheme

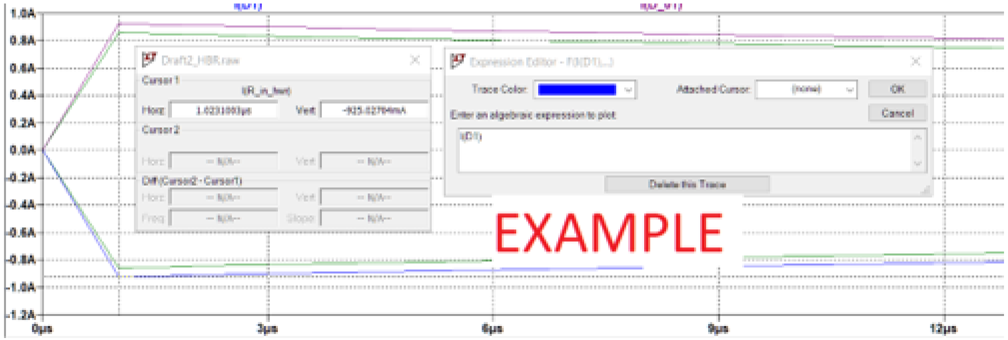


Fig 3.5 –Starting current

$$I_{VDONexp} = 2.493 \quad \text{(A)}$$

Step Five: Results

Conclusions should contain:

1) Diode check results:
- Is breakdown voltage check passed? /Is voltage source changed because of overvoltage?
- Is starting current check passed? /Is additional resistance r_vs added to prevent overcurrent in diode/capacitor?

2) Capacitor information: nominal value, tolerance, allowed current

3) Provided ripple factor value

Without filter/with filter issues

Conclusion should contain:

1) Diode check results:

- Is breakdown voltage check passed? /Is voltage source changed because of overvoltage?
- Is starting current check passed? /Is additional resistance r_vs added to prevent overcurrent in diode/capacitor?

2) Capacitor information: nominal value, tolerance, allowed current

3) Provided ripple factor value

If there are no conclusion or some parts o conclusion is missing – the score will be reduced by 1 point of 3

Evaluations

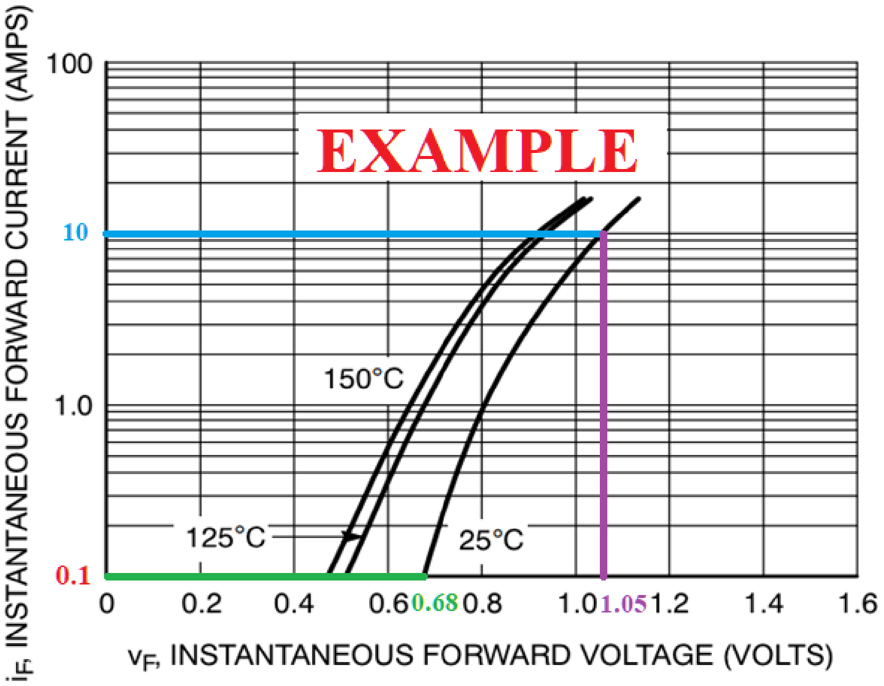
- Evaluations (pp 4.2-4.6. of the report are not obligatory, it’s optional).
- It is better to delete this parts from the report, if you didn’t fulfill this parts
- However, if you do optional parts with mistakes, were will be penalty for that, and you will have no extra points while fixes won’t be done.

If there are no conclusion or some parts o conclusion is missing – the score will be reduced by 1 point of 3

Practice task 1
Simple semiconductor device circuits design

Nikolay Nikolaev (nanikolaev@itmo.ru)
Nikolai Poliakov (polyakov_n_a@itmo.ru)
Roman Olekhnovich (r.o.olekhnovich@mail.ru)

Diode active resistance



Maximum repetitive peak surge forward current

$$I_{fwd\_imp} = 10 \qquad \text{(A)}$$

Diode forward bias voltage

$$V_{fwd\_max}\left(I_{fwd\_imp}\right) = 1.05 \qquad \text{(V)}$$

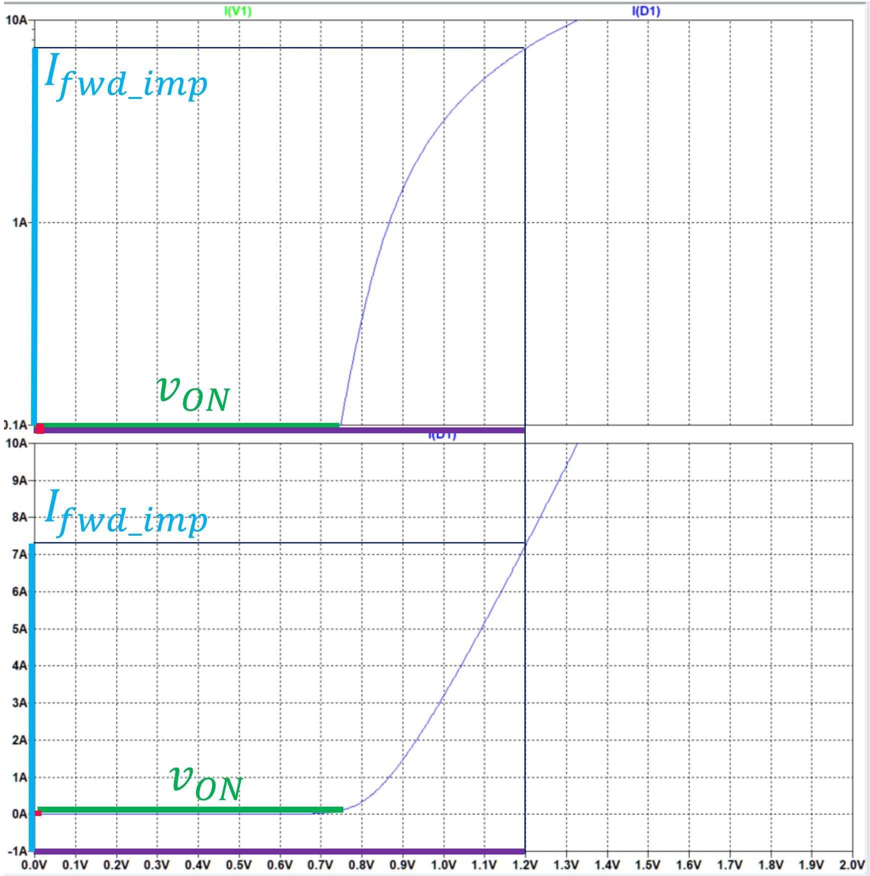
Diode threshold voltage:

$$v_{ON} = 0.68 \qquad \text{(V)}$$

Diode active resistance:

$$r_{VD} = \frac{V_{fwd\_max} - v_{ON}}{I_{fwd_{imp}} - I_{fwd}(v_{ON})} = \qquad (\Omega)$$

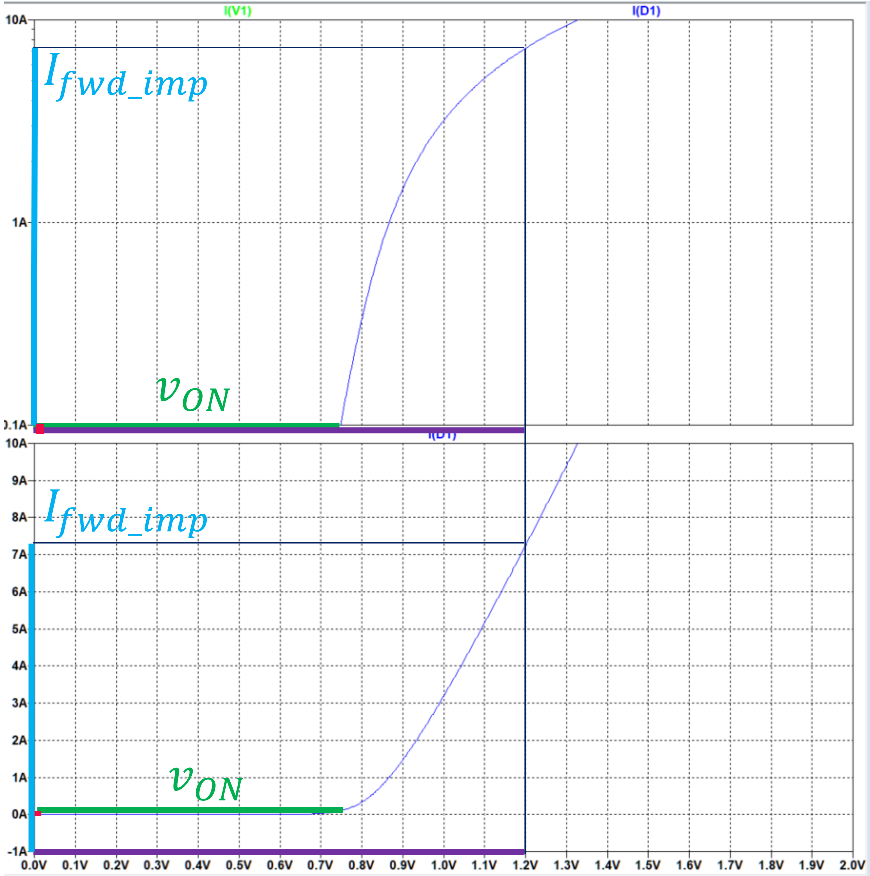
Diode active resistance

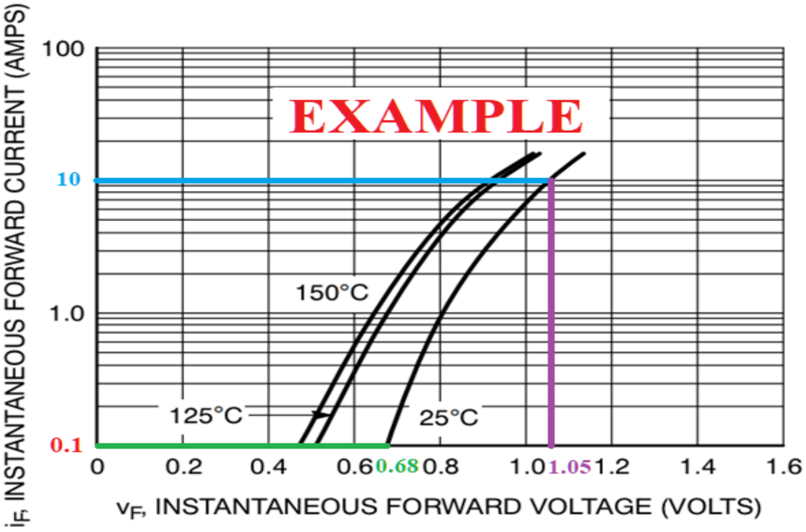


Diode active resistance:

$$r_{VD} = \frac{V_{fwd\_max} - v_{ON}}{I_{fwd_{imp}} - I_{fwd}(v_{ON})} \quad (\Omega)$$

Diode active resistance

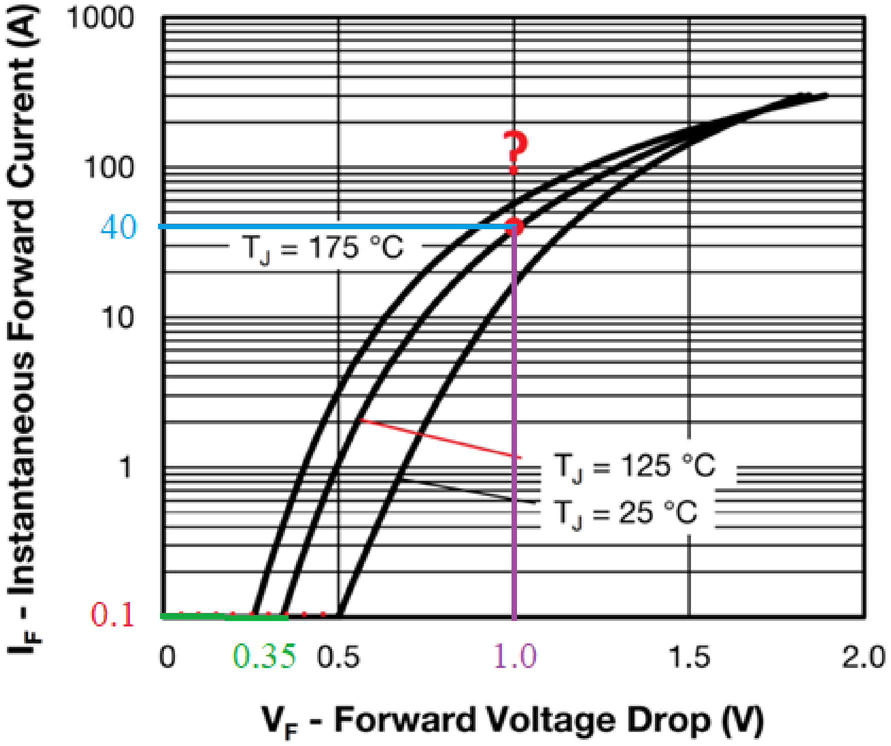




Diode current at starting conduct state:

$I_{fwd}(v_{ON}) =$ (Ω)

Diode active resistance



Maximum repetitive peak surge forward current

$$I_{fwd\_imp} = 40 \qquad \text{(A)}$$

Diode forward bias voltage

$$V_{fwd\_max}(I_{fwd\_imp}) = 1.0 \qquad \text{(V)}$$

Diode threshold voltage:

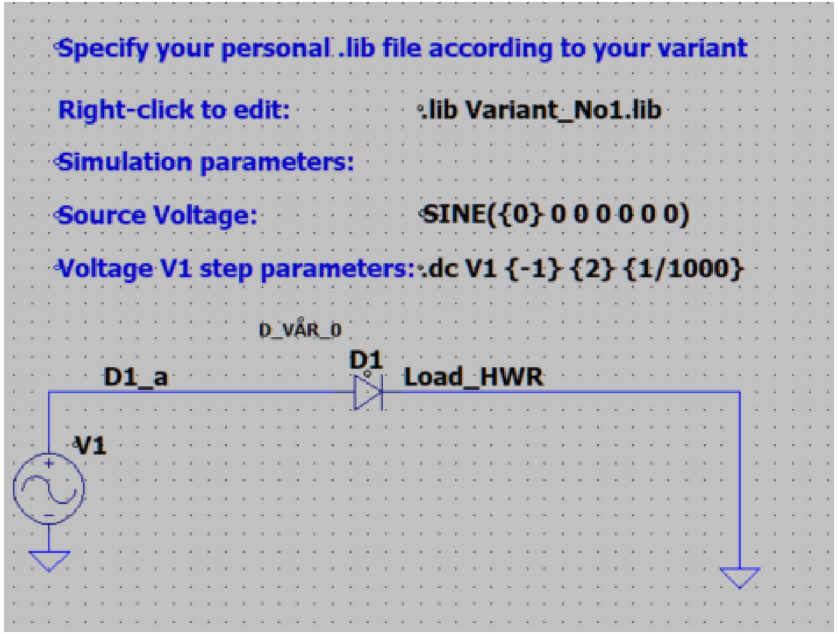
$$v_{ON} = 0.35 \qquad \text{(V)}$$

Diode active resistance:

$$r_{VD} = \frac{V_{fwd\_max} - v_{ON}}{I_{fwd_{imp}} - I_{fwd}(v_{ON})} \qquad (\Omega)$$

$$r_{VD} = \frac{1 - 0.35}{40 - 0.1} = 0.0163\ \Omega$$

Diode VI in LT Spice



Maximum repetitive peak surge forward current

$I_{fwd\_imp} =$ (A)

Diode forward bias voltage

$V_{fwd\_max}\left(I_{fwd\_imp}\right) =$ (V)

Diode threshold voltage:

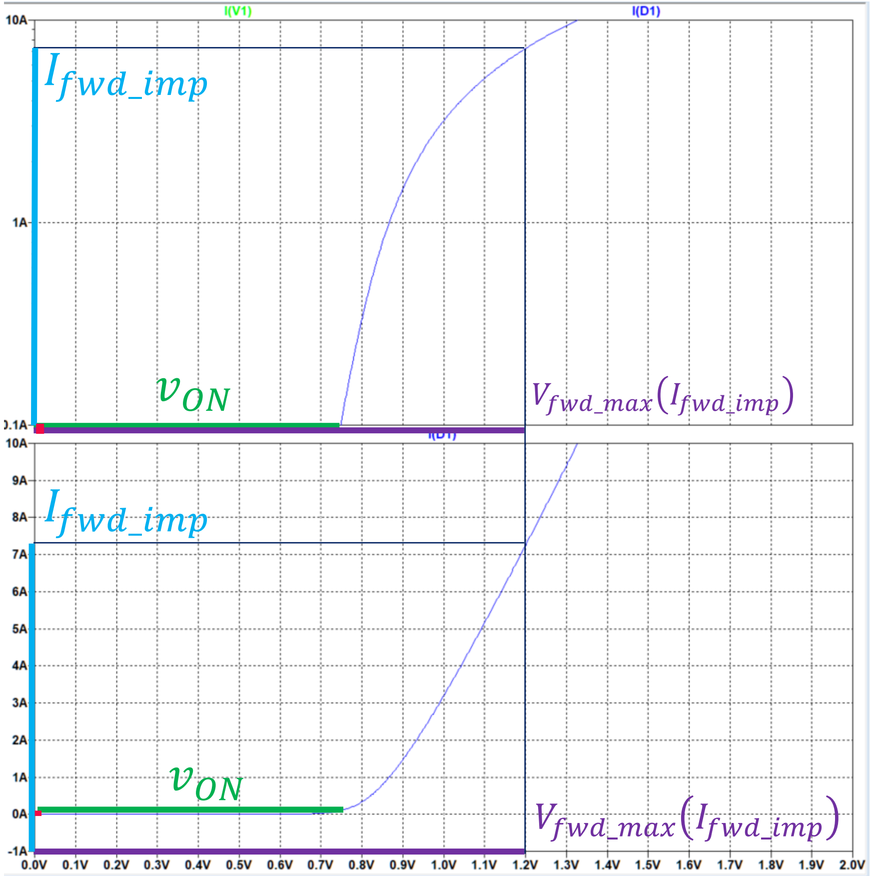
$v_{ON} =$ (V)

Diode active resistance:

$$r_{VD} = \frac{V_{fwd\_max} - v_{ON}}{I_{fwd_{imp}} - I_{fwd}(v_{ON})} \quad (\Omega)$$

$$r_{VD} = - = \quad \Omega$$

Diode active resistance



Maximum repetitive peak surge forward current

$$I_{fwd\_imp} = 7 \quad \text{(A)}$$

Diode forward bias voltage

$$V_{fwd\_max}(I_{fwd\_imp}) = 1.2 \quad \text{(V)}$$

Diode threshold voltage:

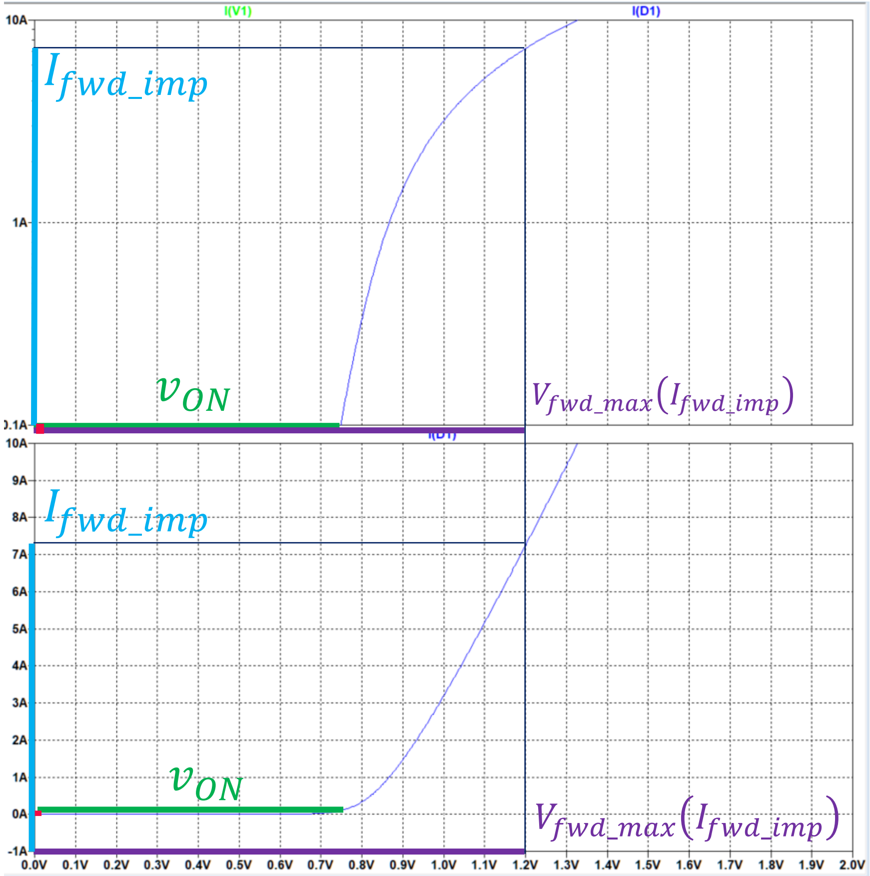
$$v_{ON} = 0.75 \quad \text{(V)}$$

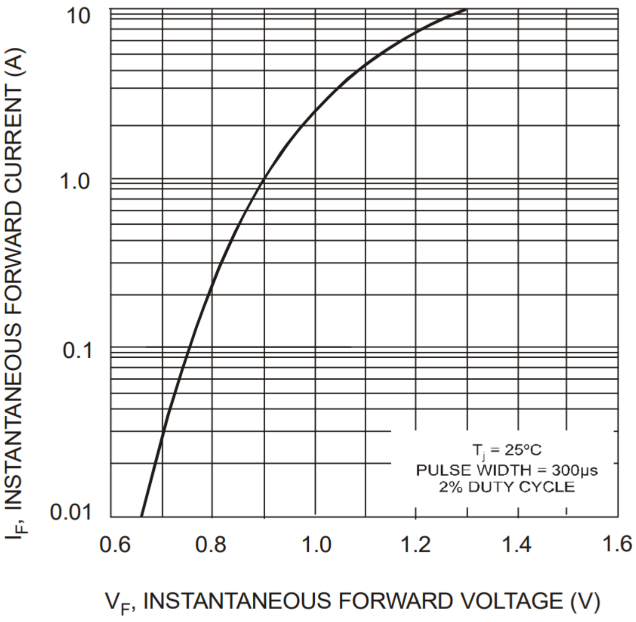
Diode active resistance:

$$r_{VD} = \frac{V_{fwd\_max} - v_{ON}}{I_{fwd_{imp}} - I_{fwd}(v_{ON})} \quad (\Omega)$$

$$r_{VD} = \frac{1.2 - 0.75}{7 - 0.1} = 0{,}065\ \Omega$$

Diode active resistance





Step Five: Submit practice results form before 1.10.2021!!

Stage III. Practice Report

Save your final LT SPICE model and upload here .zip file with your .asc file
(this is optional)

Загрузить До 20 файлов (общий размер — до 20 МБ).

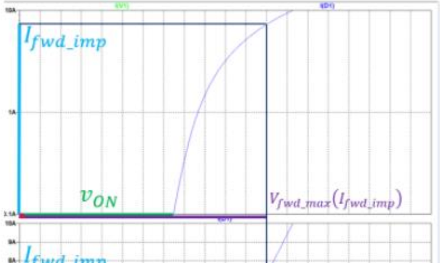
* Save a screenshot of your LTSPICE schematic

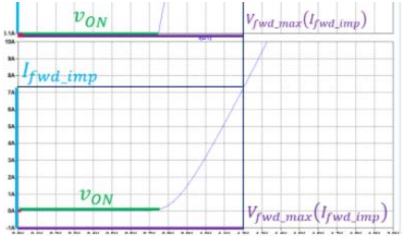
Загрузить До 20 файлов (общий размер — до 20 МБ).

* Save a screenshot of your simulation results

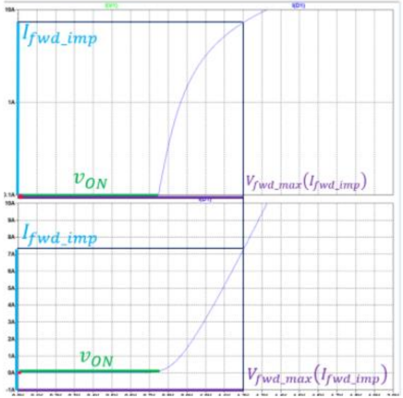
Загрузить До 20 файлов (общий размер — до 20 МБ).

Your v_on result from LT Spice





Your r_vd result from LT Spice



Назад Далее

ITMO

Thank you for your attention!